RENESAS

RL78/G1F

RENESAS MCU

Datasheet

R01DS0246EJ0112 Rev.1.12 Apr 28, 2021

True Low Power Platform (as low as 66 µA/MHz, and 0.57 µA for RTC + LVD), 1.6 V to 5.5 V operation, 32/64 Kbyte Flash, Max.32 MHz CPU operation, Enhanced analog functions, for General Purpose Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V which can operate a 1.8 V device at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 μ s: @ 32 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 μ s: @ 32.768 kHz operation with subsystem clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 MB
- General-purpose registers: (8-bit register \times 8) \times 4 banks
- On-chip RAM: 5.5 KB

Code flash memory

- Code flash memory: 32/64 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 4 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: V_{DD} = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 64 MHz, 48 MHz, 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: $\pm 1.0\%$ (V_DD = 1.8 to 5.5 V, T_{A} = -20 to +85°C)

Operating ambient temperature

- $\dot{T}_A = -40$ to +85°C (A: Consumer applications)
- T_A = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

• Event signals of 22 types can be linked to the specified peripheral function.

Serial interfaces

- CSI: 3 to 6 channels
- UART/UART (LIN-bus supported): 3 channels
- I²C/simplified I²C: 3 to 6 channels

IrDA: 1 channel

- Timer
- 16-bit timer: 9 channels
- (Timer Array Unit (TAU): 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels (with PWMOPA), Timer RG: 1 channel, Timer RX: 1 channel)
- 12-bit interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (V_{DD} = 1.6 to 5.5 V)
- Analog input: 8 to 17 channels
- Internal reference voltage (1.45 V) and temperature sensor

D/A converter

- 8-bit resolution D/A converter (V_{DD} = 1.6 to 5.5 V)
- Analog output: 1 or 2 channels
- Output voltage: 0 V to VDD
- Real-time output function

Comparator

- 2 channels (pin selector is provided for 1 channel)
- Incorporates a function for the output of a timer window in combination with the timer array unit.
- The external reference voltage or internal reference voltage can be selected as the reference voltage.

Programmable gain amplifier (PGA)

1 channel

I/O port

- I/O port: 20 to 58 (N-ch open drain I/O [withstand voltage of 6 V]: 2 to 4, N-ch open drain I/O [VDD withstand voltage/EVDD withstand voltage]: 10 to 16)
- Can be set to N-ch open drain, TTL input buffer, and onchip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3
 V device
- On-chip key interrupt function
- · On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- **Remark** The functions mounted depend on the product. See **1.6 Outline of Functions**.

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G1F						
	Data liasti		24 pins	32 pins	36 pins	48 pins	64 pins		
64 KB	4 KB	5.5 KB Note	R5F11B7E	R5F11BBE	R5F11BCE	R5F11BGE	R5F11BLE		
32 KB	4 KB	5.5 KB Note	R5F11B7C	R5F11BBC	R5F11BCC	R5F11BGC	R5F11BLC		

NoteThis is about 4.5 KB when performing self-programming and rewriting the data flash memory (For details, see CHAPTER
3 CPU ARCHITECTURE in the RL78/G1F User's Manual).



1.2 Ordering Information

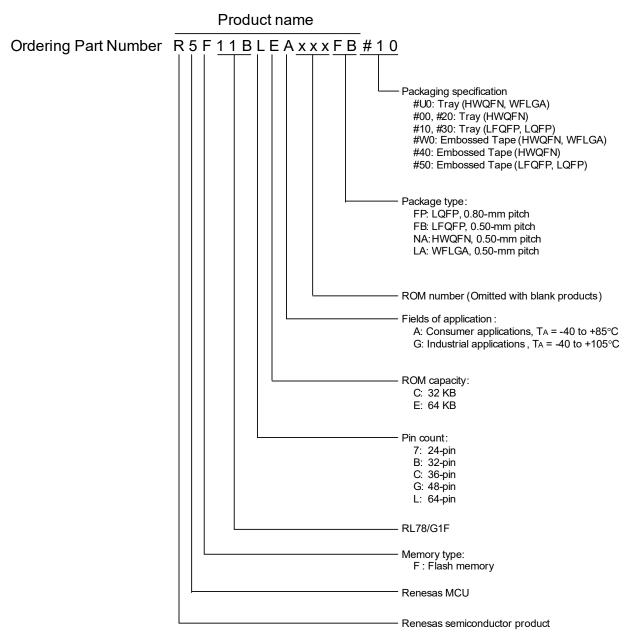


Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F



Pin		Fields of	Ordering Part Number			
count	Package	Application Note	Product name	Packaging specification	RENESAS Code	
24 pins	24-pin plastic HWQFN	A	R5F11B7CANA, R5F11B7EANA	#U0, #W0	PWQN0024KE-A	
	(4 × 4 mm, 0.5-mm pitch)			#00, #20, #40	PWQN0024KF-A	
		G	R5F11B7CGNA, R5F11B7EGNA	#U0, #W0	PWQN0024KE-A	
				#00, #20, #40	PWQN0024KF-A	
32 pins	32-pin plastic HWQFN	A	R5F11BBCANA, R5F11BBEANA	#00, #20, #40	PWQN0032KE-A	
	(5 × 5 mm, 0.5-mm pitch)	G	R5F11BBCGNA, R5F11BBEGNA			
	32-pin plastic LQFP	A	R5F11BBCAFP, R5F11BBEAFP	#10, #30, #50	PLQP0032GB-A	
	(7 × 7 mm, 0.8-mm pitch)	G	R5F11BBCGFP, R5F11BBEGFP			
36 pins	36-pin plastic WFLGA	A	R5F11BCCALA, R5F11BCEALA	#U0, #W0	PWLG0036KA-A	
	(4 × 4 mm, 0.5-mm pitch)	G	R5F11BCCGLA, R5F11BCEGLA			
48 pins	48-pin plastic LFQFP	A	R5F11BGCAFB, R5F11BGEAFB	#10, #30, #50	PLQP0048KB-B	
	(7 × 7 mm, 0.5-mm pitch)	G	R5F11BGCGFB, R5F11BGEGFB			
64 pins	64-pin plastic LFQFP	A	R5F11BLCAFB, R5F11BLEAFB	#10, #30, #50	PLQP0064KB-C	
	(10 × 10 mm, 0.5-mm pitch)	G	R5F11BLCGFB, R5F11BLEGFB	1		

Table 1	- 1	List of	Ordering	Part	Numbers
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Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

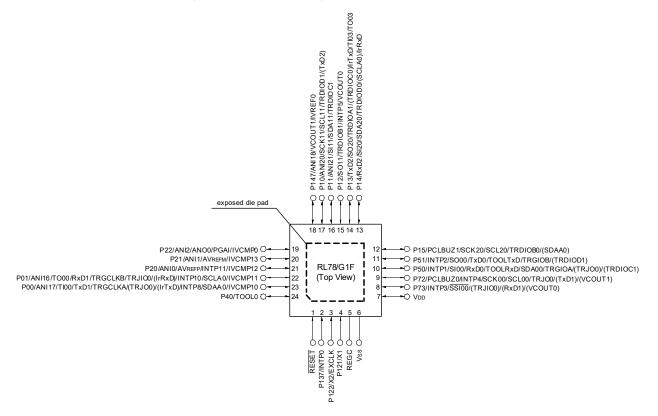
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1.3 Pin Configuration (Top View)

1.3.1 24-pin products

• 24-pin plastic HWQFN (4 × 4 mm, 0.5-mm pitch)

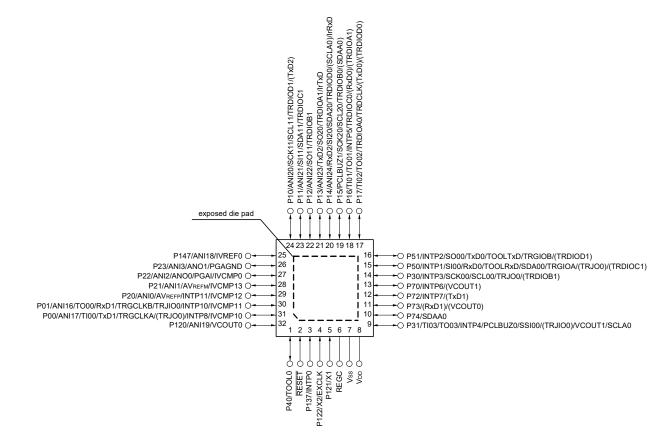


- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).



1.3.2 32-pin products

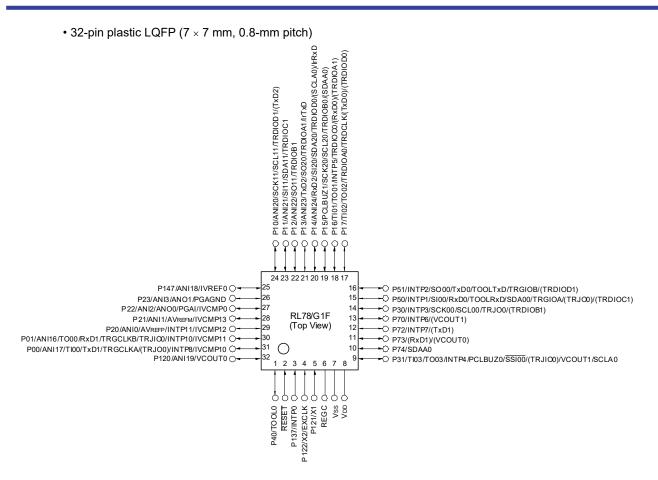
<R> • 32-pin plastic HWQFN (5 × 5 mm, 0.5-mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

- **Remark 1.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).
- Remark 2. It is recommended to connect an exposed die pad to Vss.





Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

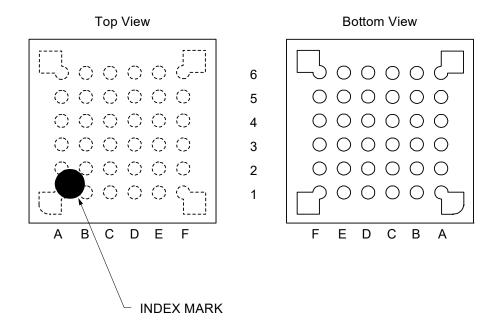
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).



1.3.3 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5-mm pitch)



	А	В	С	D	E	F	
6	EVDD0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P61/SDAA0	P60/SCLA0	Vss	REGC	RESET	P124/XT2/ EXCLKS	5
4	P31/TI03/TO03/ INTP4/PCLBUZ0/ SSI00/(TRJIO0)/ VCOUT1	P14/ANI24/RxD2/ SI20/SDA20/ TRDIOD0/ (SCLA0)/IrRxD	P20/ANI0/ AVREFP/IVCMP12/ INTP11	P21/ANI1/ AVREFM/IVCMP13	P01/ANI16/TO00/ RxD1/TRGCLKB/ TRJIO0/INTP10/ IVCMP11	P123/XT1	4
3	P50/INTP1/SI00/ RxD0/TOOLRxD/ SDA00/TRGIOA/ (TRJO0)/ (TRDIOC1)	P70/INTP6/ (VCOUT0)/ (VCOUT1)	P15/PCLBUZ1/ SCK20/SCL20/ TRDIOB0/ (SDAA0)	P23/ANI3/ANO1/ PGAGND	P00/ANI17/TI00/ TxD1/TRGCLKA/ (TRJO0)/INTP8/ IVCMP10	P120/ANI19/ VCOUT0	3
2	P30/INTP3/ RTC1HZ/SCK00/ SCL00/TRJO0/ (TRDIOB1)	P16/TI01/TO01/ INTP5/TRDIOC0/ (RxD0)/ (TRDIOA1)	P12/ANI22/SO11/ TRDIOB1	P11/ANI21/SI11/ SDA11/TRDIOC1	P24/ANI4	P22/ANI2/ANO0/ PGAI/IVCMP0	2
1	P51/INTP2/SO00/ TxD0/TOOLTxD/ TRGIOB/ (TRDIOD1)	P17/TI02/TO02/ TRDIOA0/ TRDCLK0/(TxD0)/ (TRDIOD0)	P13/ANI23/TxD2/ SO20/TRDIOA1/ IrTxD	P10/ANI20/ SCK11/SCL11/ TRDIOD1/(TxD2)	P147/ANI18/ IVREF0	P25/ANI5	1
	А	В	С	D	E	F	

Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.

Remark 1. For pin identification, see 1.4 Pin Identification.

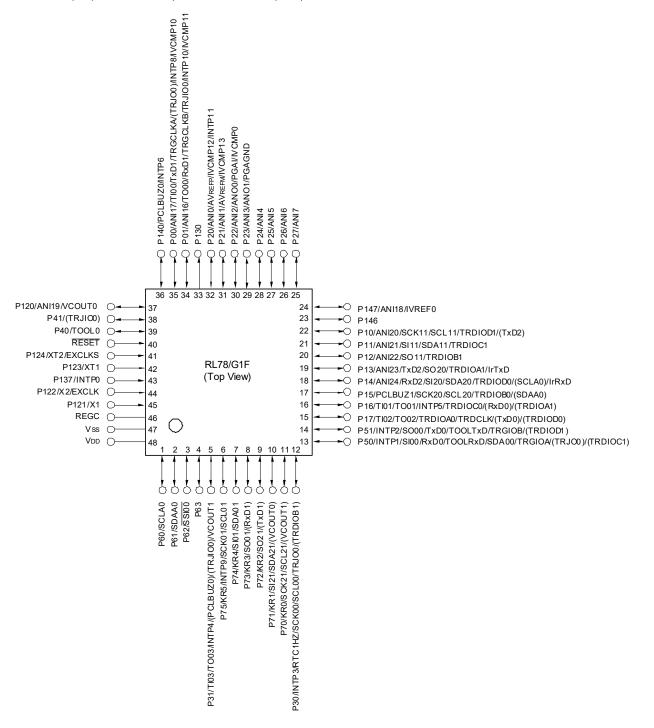
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

Remark 3. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins.

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1.3.4 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5-mm pitch)



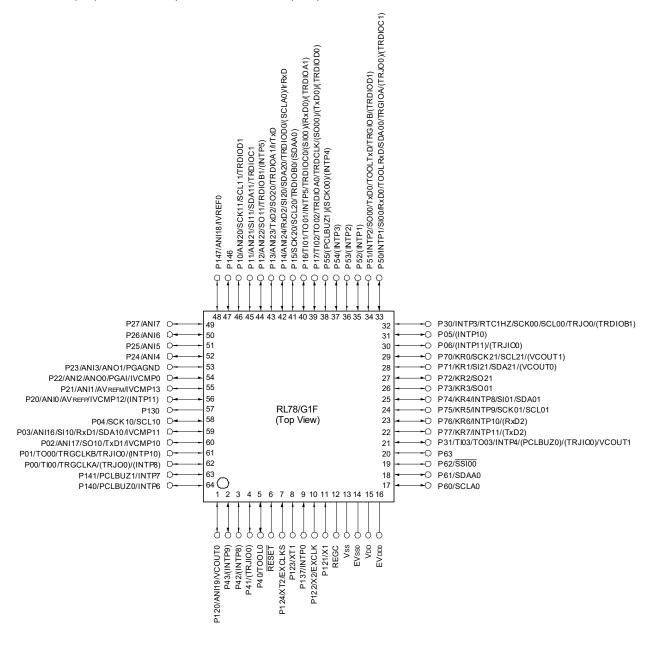
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

1.3.5 64-pin products

• 64-pin plastic LFQFP (10 × 10 mm, 0.5-mm pitch)



Caution 1. Make EVsso pin the same potential as Vss pin.

Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.

Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the VSS and EVSS0 pins to separate ground lines.

Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

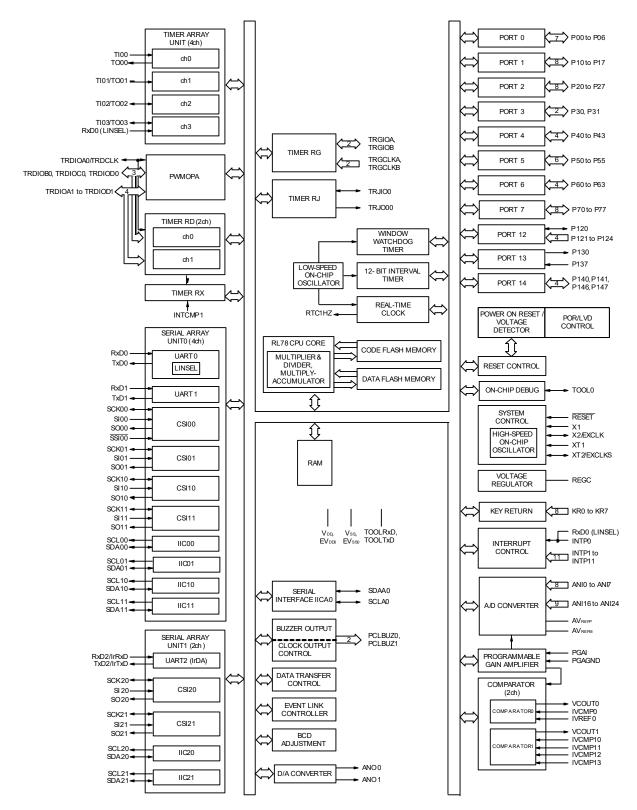


1.4 Pin Identification

ANI0 to ANI7:	Analog input	PGAI:	PGA input
ANI16 to ANI24:	Analog input	PGAGND:	PGA input
ANO0, ANO1:	Analog output	RTC1HZ:	Real-time clock correction
AVREFM:	Analog reference voltage		clock (1 Hz) output
	minus	RxD0 to RxD2:	Receive data
AVREFP:	Analog reference voltage	SCK00, SCK01, SCK10:	Serial clock input/output
	plus	SCK11, SCK20, SCK21:	Serial clock input/output
EVDD0:	Power supply for port	SCLA0:	Serial clock input/output
EVsso:	Ground for port	SCL00, SCL01, SCL10, SCL11:	Serial clock output
EXCLK:	External clock input	SCL20,SCL21:	Serial clock output
	(main system clock)	SDAA0:	Serial data input/output
EXCLKS:	External clock input	SDA00, SDA01, SDA10:	Serial data input/output
	(subsystem clock)	SDA11, SDA20, SDA21:	Serial data input/output
INTP0 to INTP11:	External interrupt input	SI00, SI01, SI10, SI11:	Serial data input
lrRxD:	Receive Data for IrDA	SI20, SI21:	Serial data input
lrTxD:	Transmit Data for IrDA	SO00, SO01, SO10:	Serial data output
IVCMP0:	Comparator 0 input	SO11, SO20, SO21:	Serial data output
IVCMP10 to IVCMP13:	Comparator 1 input /	SSI00:	Serial interface chip select input
	reference input	TI00 to TI03:	Timer input
IVREF0:	Comparator 0 reference	TO00 to TO03:	Timer output
	input	TRJO0:	Timer output
KR0 to KR7:	Key return	TOOL0:	Data input/output for tool
P00 to P06:	Port 0	TOOLRxD, TOOLTxD:	Data input/output for external device
P10 to P17:	Port 1	TRDCLK, TRGCLKA:	Timer external input clock
P20 to P27:	Port 2	TRGCLKB:	Timer external Input clock
P30, P31:	Port 3	TRDIOA0, TRDIOB0:	Timer input/output
P40 to P43:	Port 4	TRDIOC0, TRDIOD0:	Timer input/output
P50 to P55:	Port 5	TRDIOA1, TRDIOB1:	Timer input/output
P60 to P63:	Port 6	TRDIOC1, TRDIOD1:	Timer input/output
P70 to P77:	Port 7	TRGIOA, TRGIOB, TRJIO0:	Timer input/output
P120 to P124:	Port 12	TxD0 to TxD2:	Transmit data
P130, P137	Port 13	VCOUT0, VCOUT1:	Comparator output
P140, P141, P146,	Port 14	Vdd:	Power supply
P147:		Vss:	Ground
PCLBUZ0, PCLBUZ1:	Programmable clock output/	X1, X2:	Crystal oscillator (main system clock)
	buzzer output	XT1, XT2:	Crystal oscillator (subsystem clock)
REGC:	Regulator capacitance		
RESET:	Reset		



1.5 Block Diagram



Remark Block diagram of 64-pin products is shown as an example. For difference of the block diagram other than 64-pin products, refer to **1.6 Outline of Functions**.



1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

	(FIORU, I) are set to					(1/2			
		24-pin	32-pin	36-pin	48-pin	64-pin			
Item		R5F11B7x (x = C, E)	R5F11BBx (x = C, E)	R5F11BCx (x = C, E)	R5F11BGx (x = C, E)	R5F11BLx (x = C, E)			
Code flash mer	mory (KB)	32, 64	32, 64	32, 64	32, 64	32, 64			
Data flash men	nory (KB)	4	4	4	4	4			
RAM (KB)		5.5 Note	5.5 Note	5.5 Note	5.5 Note	5.5 Note			
Address space	!	1 MB							
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 2.7 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 1.8 V)							
	High-speed on-chip oscillator clock (fiн)	HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)							
Subsystem clo	ck	-	_	XT1 (crystal) oscillat (EXCLKS) 32.768 kl	tion, external subsyst Hz	em clock input			
Low-speed on-	chip oscillator clock	15 kHz (TYP.): VDD :	= 1.6 to 5.5 V						
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)							
Minimum instru	uction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)							
		0.05 μs (High-speed	d system clock: fмx = :	20 MHz operation)					
		-	_	30.5 µs (Subsystem	clock: fsue = 32.768	kHz operation)			
Instruction set		 Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 							
I/O port	Total	20	28	31	44	58			
	CMOS I/O	17 (N-ch O.D. output [Vbb withstand voltage]: 10)	25 (N-ch O.D. output [V _{DD} withstand voltage]: 12)	24 (N-ch O.D. output [V _{DD} withstand voltage]: 10)	34 (N-ch O.D. output [V _{DD} withstand voltage]: 12)	48 (N-ch O.D. output [Vpd withstand voltage]: 12)			
	CMOS input	3	3	5	5	5			
	CMOS output	—	_	—	1	1			
	N-ch open-drain I/O (6 V tolerance)	_	_	2	4	4			
Timer	16-bit timer	9 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels (with PWMOPA), Timer RX: 1 channel, Timer RG: 1 channel)							
	Watchdog timer	1 channel							
	Real-time clock (RTC)	1 channel							
	12-bit interval timer	1 channel							
	Timer output	Timer outputs: 13 channels PWM outputs:	Timer outputs: 16 channels PWM outputs:						
		8 channels	9 channels						

Note

This is about 4.5 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G1F User's Manual).

		24-pin	32-pin	36-pin	48-pin	(2 64-pin		
Item		R5F11B7x	R5F11BBx	R5F11BCx	R5F11BGx	R5F11BLx		
		(x = C, E)	(x = C, E)	(x = C, E)	(x = C, E)	(x = C, E)		
Clock output/buzzer	output	2	2	2	2	2		
			z, 9.76 kHz, 1.25 MH: k: fmain = 20 MHz оре		0 MHz			
8/10-bit resolution A/	D converter	8 channels	13 channels	15 channels	17 channels	17 channels		
8-bit D/A converter		1 channel		2 cha	nnels			
Comparator				2 channels				
Programmable gain a	amplifier (PGA)			1 channel				
Serial interface		 [24-pin, 32-pin, 36-pin products] CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified l²C: 1 channel CSI: 1 channel/UART: 1 channel/simplified l²C: 1 channel CSI: 1 channel/UART: 1 channel/simplified l²C: 1 channel [48-pin products] CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified l²C: 2 channels CSI: 2 channels/UART: 1 channel/simplified l²C: 1 channel CSI: 2 channels/UART: 1 channel/simplified l²C: 2 channels [64-pin products] CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified l²C: 2 channels [64-pin products] CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified l²C: 2 channels [64-pin products] CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified l²C: 2 channels 						
	I ² C bus	CSI: 2 channels/0. 1 channel	ART: 1 channel/simpl 1 channel	1 channel	1 channel	1 channel		
Data transfer controll	er (DTC)	30 sources	32 sources	31 sources	32 sources	33 sources		
Event link controller	Event input	21	21	21	22	22		
(ELC)	Event trigger output	9	10	10	10	10		
Vectored interrupt	Internal	25	25	25	25	25		
sources	External	9	11	10	12	13		
Key interrupt			_	_	6	8		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution ^{Note} Internal reset by RAM parity error Internal reset by illegal-memory access						
Power-on-reset circu	it	 Power-on-reset: 1.51 ±0.04 V (Ta = -40 to +85°C) 1.51 ±0.06 V (Ta = -40 to +105°C) Power-down-reset: 1.50 ±0.04 V (Ta = -40 to +85°C) 1.50 ±0.06 V (Ta = -40 to +105°C) 						
Voltage detector		 Falling edge: 1.63 [TA = -40 to +105°C Rising edge: 2.61 	±0.03 V to 4.00 ±0.08 ±0.03 V to 3.98 ±0.04 (G: Industrial applica ±0.1 V to 4.06 ±0.16 ±0.1 V to 3.98 ±0.15	3 V (14 stages) tions)] V (8 stages)				
On-chip debug functi	on	Provided		•				
Power supply voltage	2	VDD = 1.6 to 5.5 V (T VDD = 2.4 to 5.5 V (T	,					
Operating ambient temperature		T _A = -40 to +85°C (A	A. Consumer applicat	ions) $T_{A} = -40$ to +10)5°C (Industrial appli	cations)		

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^{\circ}C$

R5F11BxxAxx

- G: Industrial applications when $T_A = -40$ to $+105^{\circ}$ C products is used in the range of $T_A = -40$ to $+85^{\circ}$ C R5F11BxxGxx
- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVss0 pin, replace EVDD0 with VDD, or replace EVss0 with Vss.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G1F User's Manual.



(1/2)

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD0		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V _{DD} +0.3 ^{Note 1}	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	P20 to P27, P121 to P124, P137, EXCLK, EXCLKS, RESET	-0.3 to VDD +0.3 Note 2	V
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 ^{Note 2}	V
	Vo2	P20 to P27	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI24	-0.3 to EVDD0 +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	v
	VAI2	ANI0 to ANI7	-0.3 to VDD +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage



Absolute Maximum Ratings

(2/2)

	anngo				(2/
Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147	-40	mA
		Total of all	P00 to P04, P40 to P43,P120, P130, P140, P141	-70	mA
		pins -170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40-P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	40	mA
	pir	Total of all	P00 to P04, P40 to P47, P120, P130, P140, P141	70	mA
		pins 170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	100	mA
	IOL2	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient tem-	Та	In normal c	pperation mode	-40 to +85	°C
perature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.



2.2 Oscillator Characteristics

2.2.1 X1, XT1 characteristics

(TA = -40 to +85°C, 1.6 V \leq EV_{DD0} = VDD \leq 5.5 V, Vss = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V \text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{V}\text{DD} < 2.7~\text{V}$	1.0		16.0	
		$1.8~V \leq V_{DD} < 2.4~V$	1.0		8.0	
		$1.6~V \leq V_{DD} < 1.8~V$	1.0		4.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +85°C, 1.6 V \leq EV_{DD0} = VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Cor	nditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fiн	$2.7~V \le V_{DD} \le 5.5~V_{DD}$	V	1		32	MHz
Notes 1, 2		$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	V	1		16	MHz
		$1.8 \text{ V} \leq \text{V}_{DD} < 2.4 \text{ V}_{DD}$	V	1		8	MHz
		$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$		1		4	MHz
High-speed on-chip oscillator clock frequency		TA = -20 to +85°C	$1.8~V \leq V\text{DD} \leq 5.5~V$	-1		1	%
accuracy			$1.6 \text{ V} \le \text{V}_{\text{DD}}$ < 1.8 V	-5		5	%
		TA = -40 to -20°C	$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 5.5 \text{ V}$	-1.5		1.5	%
			$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 1.8 \text{ V}$	-5.5		5.5	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1F User's Manual.

2.3 DC Characteristics

2.3.1 Pin characteristics

(TA = -40 to +85°C,	1.6 $V \leq EVDD0$	\leq VDD \leq 5.5 V. VSS	= EVsso = 0 V
(,	

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	P10 to P17, P30, P31, P40 to P47, P50 to P55,	P10 to P17, P30, P31, P40 to P47, P50 to P55, P70 to P77, P120, P130, P140,				-10.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-55.0	mA
		(When duty ≤ 70% ^{Note 3}) Total of P05, P06, P10 to P17, P30, P31, P50 to P53,	$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-5.0	mA
			$1.6~V \leq EV_{DD0} < 1.8~V$			-2.5	mA
			$4.0~V \leq EV \text{dd} \leq 5.5~V$			-80.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		P70 to P77, P146, P147 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \leq EV_{DD0} < 2.7 \text{ V}$			-10.0	mA
			$1.6~V \leq EV_{DD0} < 1.8~V$			-5.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				-135.0 Note 4	mA
	IOH2 Per pin for P20 to P27				-0.1 Note 2	mA	
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6~V \leq V\text{DD} \leq 5.5~V$			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, VDD pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$ <Example> Where n = 80% and IOH = -10.0 mA Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Note 4. The applied current for the products for industrial application (R5F11BxxGxx) is -100 mA.
- Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.
- Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77,P120, P130, P140, P141, P146, P147 Per pin for P60 to P63				20.0 Note 2 15.0	mA mA
		Total of P00 to P04, P40 to P43,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			Note 2 70.0	mA
		P120, P130, P140, P141	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			15.0	mA
		(When duty \leq 70% ^{Note 3})	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV \text{DD0} \leq 5.5~V$			80.0	mA
		P30, P31, P50 to P55, P60 to	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P63, P70 to P77, P146, P147 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			20.0	mA
		(when duly $\leq 70\%$ has s)	$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty \leq 70% ^{Note 3})				150.0	mA
	IOL2	Per pin for P20 to P27				0.4 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$1.6~V \le V \text{DD} \le 5.5~V$			5.0	mA

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/5)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOL \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Items nput voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0.8 EVDD0		EVDD0	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	2.2		EVDD0	V
nput voltage, high			TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}$	1.5		EVDD0	V
	VIH3	P20 to P27 (when P20 is used as	a port pin)	0.7 Vdd		Vdd	V
	VIH4	P60 to P63		0.7 EVDD0		6.0	V
nput voltage, low	Vih5	P121 to P123, P137, EXCLK, EX P20 is used as INTP11 pin)	0.8 Vdd		Vdd	V	
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	1, P40 to P43, P50 to P55, 0 to P77, P120, P140, P141,			0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}$	0		0.32	V
	VIL3	P20 to P27 (when P20 is used as	a port pin)	0		0.3 Vdd	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	Vil5	P121 to P124, P137, EXCLK, EX P20 is used as INTP11 pin)	CLKS, RESET (when	0		0.2 Vdd	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(3/5)

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 is EVDD0, even in the N-ch open-drain mode.



Items	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Output voltage, high	Voh1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -10.0 mA	EVDD0 - 1.5			V
		P70 to P77, P120, P130, P140, P141, P146, P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
			2.7 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -2.0 mA	EVDD0 - 0.6			V
			1.8 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EVppo < 1.8 V, Іон1 = -1.0 mA	EVDD0 - 0.5			V
	Voh2	P20 to P27	1.6 V ≤ Vdd ≤ 5.5 V, Ioh2 = -100 μA	Vdd - 0.5			V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OL1} = 20.0 \ mA \end{array}$			1.3	V
		P70 to P77, P120, P130, P140, P141, P146, P147	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OL1} = 8.5 \ mA \end{array}$			0.7	V
			$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \\ \text{I}_{\text{OL1}} = 3.0 \ \text{mA} \end{array}$			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 1.5 mA			0.4	V
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OL1} = 0.6 \ mA \end{array}$			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $\text{IOL1} = 0.3 \text{ mA}$			0.4	V
	Vol2	P20 to P27	$\begin{array}{l} 1.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}, \\ \text{Iol2} = 400 \ \mu\text{A} \end{array}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 15.0 mA			2.0	V
			$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OL3} = 5.0 \ mA \end{array}$			0.4	V
			$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{IoL3} = 3.0 \ \text{mA} \end{array}$			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 2.0 mA			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OL3}} = 1.0 \text{ mA}$			0.4	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(4/5)

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.



Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVDD0				1	μΑ
	ILIH2	P20 to P27, P137, RESET	VI = VDD				1	μA
	Іцнз	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
	In resonator con- nection		10	μA				
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, RESET	VI = VSS				-1	μA
	Ilil3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator con- nection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso,	In input port	10	20	100	kΩ

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(5/5)



2.3.2 Supply current characteristics

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Un
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	VDD = 5.0 V		2.4		mA
ourrent Note 1		ing mode	mode Note 5	fiH = 32 MHz Note 3	operation	V _{DD} = 3.0 V		2.4		
NOLE I				fносо = 32 MHz,	Basic	VDD = 5.0 V		2.1		
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.1		
			HS (high-speed main)	fносо = 64 MHz,	Normal	VDD = 5.0 V		5.2	8.7	mÆ
			mode Note 5	fiн = 32 MHz Note 3	operation	VDD = 3.0 V		5.2	8.7	
				fносо = 32 MHz,	Normal	VDD = 5.0 V		4.8	8.1	1
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		4.8	8.1	
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.1	6.9	1
		fiH = 24 MHz Note 3	operation	VDD = 3.0 V		4.1	6.9			
		fносо = 24 MHz,	Normal	VDD = 5.0 V		3.8	6.3	1		
				fiн = 24 MHz Note 3	operation	VDD = 3.0 V		3.8	6.3	
				fносо = 16 MHz,	Normal	VDD = 5.0 V		2.8	4.6	1
				fiн = 16 MHz ^{Note 3}	operation	VDD = 3.0 V		2.8	4.6	
			LS (low-speed main)	fносо = 8 MHz,	Normal	VDD = 3.0 V		1.3	2.1	m
			mode Note 5	fiH = 8 MHz Note 3	operation	VDD = 2.0 V		1.3	2.1	
			LV (low-voltage main)	fносо = 4 MHz,	Normal	VDD = 3.0 V		1.3	1.9	m
	mode Note 5	fiH = 4 MHz Note 3	operation	VDD = 2.0 V		1.3	1.9	1		
	HS (high-speed main)	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.3	5.3	n		
		mode Note 5	VDD = 5.0 V	operation	Resonator connection		3.5	5.5	1	
				f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.3	5.3	İ
				VDD = 3.0 V	operation	Resonator connection		3.5	5.5	1
				f _{MX} = 10 MHz Note 2,NormalV _{DD} = 5.0 Voperation	Normal	Square wave input		2	3.1	t
					operation	Resonator connection		2.1	3.2	-
				f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		2	3.1	İ
				VDD = 3.0 V	operation	Resonator connection		2.1	3.2	
			LS (low-speed main)	f _{MX} = 8 MHz ^{Note 2} ,	Normal	Square wave input		1.2	1.9	n
			mode Note 5	VDD = 3.0 V	operation	Resonator connection		1.2	2	
				f _{MX} = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	ł
				VDD = 2.0 V	operation	Resonator connection		1.2	2	
			Subsystem clock	fsub = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μ
			operation	$T_A = -40^{\circ}C$	operation	Resonator connection		4.7	6.1	1
				fsub = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	ł
			$T_A = +25^{\circ}C$	operation	Resonator connection		4.7	6.1		
		fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	ł		
			$T_A = +50^{\circ}C$	operation	Resonator connection		4.8	6.7	1	
				fs∪в = 32.768 kHz ^{Note 4}	Normal	Square wave input		4.8	7.5	ł
				$T_A = +70^{\circ}C$	operation	Resonator connection		4.8	7.5	
				fsuв = 32.768 kHz ^{Note 4}	Normal	Square wave input		5.4	8.9	ł
				$T_A = +85^{\circ}C$	operation	Resonator connection		5.4	8.9	1

(TA = -40 to +85°C	, 1.6 V \leq EVDD0 \leq VDD \leq 5.5	V, Vss = EVsso = 0 V
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(Notes and Remarks are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$ @1 MHz to 32 MHz
	2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz

- LV (low-voltage main) mode: $1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 4 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- **Remark 3.** fill: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fносо = 64 MHz,	VDD = 5.0 V		0.8	3.09	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	VDD = 3.0 V		0.8	3.09	1
				fносо = 32 MHz,	VDD = 5.0 V		0.54	2.4	1
				fiн = 32 MHz Note 4	VDD = 3.0 V		0.54	2.4	1
				fносо = 48 MHz,	VDD = 5.0 V		0.62	2.4	1
				fiн = 24 MHz Note 4	VDD = 3.0 V		0.62	2.4	1
				fносо = 24 MHz,	VDD = 5.0 V		0.44	1.83	1
				fiH = 24 MHz Note 4	VDD = 3.0 V		0.44	1.83	1
				fносо = 16 MHz,	VDD = 5.0 V		0.4	1.38	1
				fiн = 16 MHz ^{Note 4}	VDD = 3.0 V		0.4	1.38	1
			LS (low-speed main)	fносо = 8 MHz,	VDD = 3.0 V		260	790	μA
			mode Note 7	fiH = 8 MHz Note 4	VDD = 2.0 V		260	790	
			LV (low-voltage main)	fносо = 4 MHz,	VDD = 3.0 V		420	830	μA
			mode Note 7	fiH = 4 MHz Note 4	VDD = 2.0 V		420	830	
			HS (high-speed main)	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.55	mA
			mode Note 7	VDD = 5.0 V	Resonator connection		0.49	1.74	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.55	
				VDD = 3.0 V	Resonator connection		0.49	1.74	
		f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.86			
				VDD = 5.0 V	Resonator connection		0.3	0.93	
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.86	
				VDD = 3.0 V	Resonator connection		0.3	0.93	
			LS (low-speed main) mode ^{Note 7}	fmx = 8 MHz Note 3,	Square wave input		95	640	μA
		mode ^{Note 7}		V _{DD} = 3.0 V	Resonator connection		145	680	
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		95	640	
				VDD = 2.0 V	Resonator connection		145	680	1
			Subsystem clock	fsue = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μA
			operation	TA = -40°C	Resonator connection		0.44	0.76	
				fsub = 32.768 kHz Note 5,	Square wave input		0.3	0.57	
				TA = 25°C	Resonator connection		0.49	0.76	
				fsue = 32.768 kHz ^{Note 5} ,	Square wave input		0.36	1.17	
				TA = 50°C	Resonator connection		0.59	1.36	
				fsub = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
			TA = 70°C	Resonator connection		0.72	2.16		
			fsub = 32.768 kHz Note ⁵ ,	Square wave input		0.97	3.37		
			TA = 85°C	Resonator connection		1.16	3.56		
	IDD3	STOP mode	TA = -40°C				0.18	0.51	μA
	Note 6	Note 8	T _A = +25°C				0.24	0.51	
			TA = +50°C				0.29	1.1	
			TA = +70°C				0.41	1.9	
			TA = +85°C				0.9	3.3	

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)

(Notes and $\ensuremath{\textit{Remarks}}$ are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- **Note 2.** During HALT instruction execution by flash memory.
- **Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $$1.8~V \le V \mbox{DD} \le 5.5~V \ensuremath{\textcircled{0}}1~\mbox{MHz}$ to 8 MHz
 - LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}_{\textcircled{O}}1 \text{ MHz}$ to 4 MHz
- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- **Remark 3.** fill: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscilla- tor operating current	I _{FIL} Note 1				0.2		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operat- ing current	IIT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μA
A/D converter operating cur- rent	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	ADREF Note 1				75		μA
Temperature sensor operat- ing current	ITMPS Note 1				75		μA
D/A converter operating cur- rent	IDAC Notes 1, 11	Per D/A converter channel				1.5	mA
PGA operating current		Operation			480	700	μA
Comparator operating cur- rent	ICMP Notes 1, 12	Operation (per comparator chan- nel, constant current for compara-	When the internal reference voltage is not in use		50	100	μA
		tor included)	When the internal reference voltage is in use		60	110	μA
LVD operating current	ILVD Notes 1, 7				0.08		μA
Self-programming operat- ing current	IFSP Notes 1, 9				2.5	12.2	mA
BGO operating current	IBGO Notes 1, 8				2.5	12.2	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.5	0.6	mA
			The A/D conversion opera- tions are performed, Low volt- age mode, $AV_{REFP} = V_{DD} = 3.0 V$		1.2	1.44	
		CSI/UART operation			0.7	0.84	ĺ
		DTC operation			3.1		İ

(TA = -40 to +85°C	, 1.6 V \leq EVDD0	\leq VDD \leq 5.5 V,	Vss = EVsso = 0 V)
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Note 1. Current flowing to VDD.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

- **Note 3.** Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **Note 7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing during programming of the data flash.
- **Note 9.** Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 26.3.3 SNOOZE mode in the RL78/G1F User's Manual.

- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- **Remark 4.** Temperature condition of the TYP. value is $TA = 25^{\circ}C$



2.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Тсү	Main system	HS (high-speed main)	$2.7~V \leq V\text{DD} \leq 5.5~V$	0.03125		1	μs
imum instruction exe-		clock (fmain)	mode	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	0.0625		1	μs
cution time)		operation	LS (low-speed main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.125		1	μS
			LV (low-voltage main) mode	$1.6~V \leq V_{DD} \leq 5.5~V$	0.25		1	μs
		Subsystem clo	ock (fsub) operation	$1.8~V \leq V\text{DD} \leq 5.5~V$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.03125		1	μs
		program-	mode	$2.4~\text{V} \leq \text{V}_\text{DD} < 2.7~\text{V}$	0.0625		1	μs
		ming mode	LS (low-speed main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.125		1	μs
External oustern alsoli			LV (low-voltage main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.25		1	μs
External system clock	fEX	$2.7~V \leq V \text{DD} \leq$	5.5 V		1.0		20.0	MHz
frequency		$2.4~V \leq V \text{DD} \leq$	2.7 V		1.0		16.0	MHz
		$1.8 \text{ V} \le \text{V}_{DD}$ <	2.4 V		1.0		8.0	MHz
		$1.6 \text{ V} \le \text{V}_{DD}$ <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock	texн, texL	$2.7~V \leq V \text{DD} \leq$	5.5 V		24			ns
input high-level width,		$2.4~V \leq V \text{DD} \leq$	2.7 V		30			ns
low-level width		$1.8 \text{ V} \le \text{V}_{\text{DD}}$ <	2.4 V		60			ns
		$1.6 \text{ V} \le \text{V}_{\text{DD}}$ <	1.8 V		120			ns
	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low- level width	ttiH, tti∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7~V \leq EV \text{DD0} \leq 5.5~V$	100			ns
				$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	300			ns
				$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	500			ns
Timer RJ input high-	tтлн,	TRJIO		$2.7~V \leq EV \text{DD0} \leq 5.5~V$	40			ns
level width, low-level	t⊤ji∟			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	120			ns
width				1.6 V ≤ EVDD0 < 1.8 V	200			ns

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Note The following conditions are required for low voltage interface when EVDD0 < VDD1.8 V $\leq EVDD0 < 2.7$ V: MIN. 125 ns

 $1.6~\text{V} \leq \text{EV}_{\text{DD0}}$ < 1.8 V: MIN. 250 ns

RemarkfMCK: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel
number (n = 0 to 3))



$1A = -40 (0 + 65 C, 1.0 V \le EVDD \le 0.0 V, 0.05 = EV3.00 = 0 V) $ (21)							
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tтdiн, tтdi∟	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/fськ			ns
Timer RD forced cutoff signal input low-level width	TDSIL	P130/INTP0	$2MHz < fclk \le 32 MHz$	1			μs
			$f_{CLK} \leq 2 \; MHz$	1/fськ + 1			
Timer RG input high-level width, low-level width	tтGін, tтGі∟	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	fro	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LS (low-speed main) mode	$1.8~V \leq EV_{DD0} \leq 5.5~V$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LV (low-voltage main) mode	$1.6~V \leq EV_{DD0} \leq 5.5~V$			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	fPCL	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
			$2.7~V \leq EV_{DD0} < 4.0~V$			8	MHz
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 2.7 \text{ V}$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LS (low-speed main) mode	$1.8~V \leq EV_{DD0} \leq 5.5~V$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
		LV (low-voltage main) mode	$1.8~V \leq EV_{DD0} \leq 5.5~V$			4	MHz
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			2	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0	$1.6~V \le V \text{DD} \le 5.5~V$	1			μs
		INTP1 to INTP11	$1.6~V \leq EV_{DD0} \leq 5.5~V$	1			μs
Key interrupt input low-level width	tкr	KR0 to KR7	$1.8~V \le EV_{DD0} \le 5.5~V$	250			ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	1			μs
RESET low-level width	tRSL			10			μs

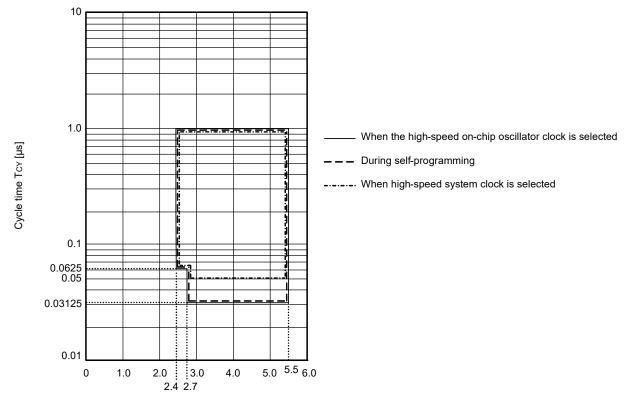
(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)



Minimum Instruction Execution Time during Main System Clock Operation

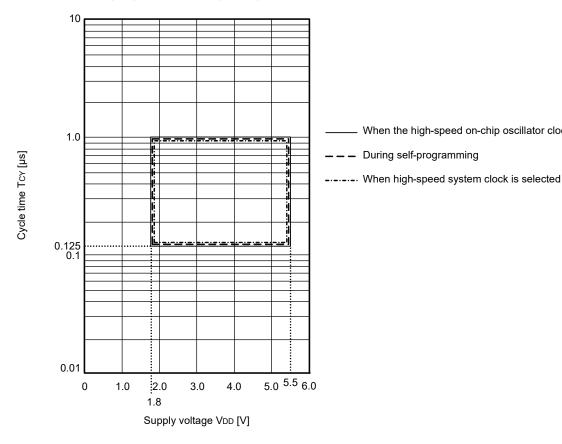
TCY vs VDD (HS (high-speed main) mode)



Supply voltage VDD [V]

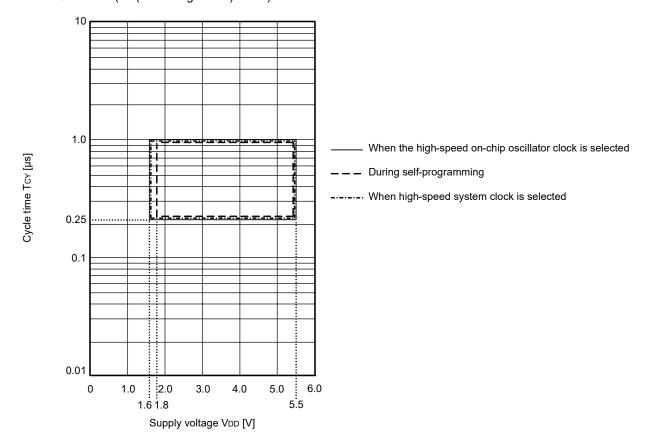


When the high-speed on-chip oscillator clock is selected



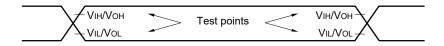
TCY vs VDD (LS (low-speed main) mode)

TCY vs VDD (LV (low-voltage main) mode)

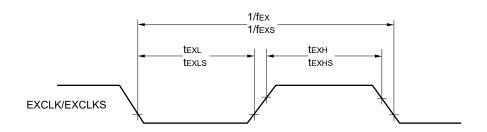




AC Timing Test Points

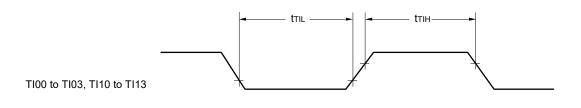


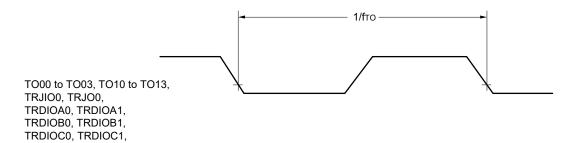
External System Clock Timing



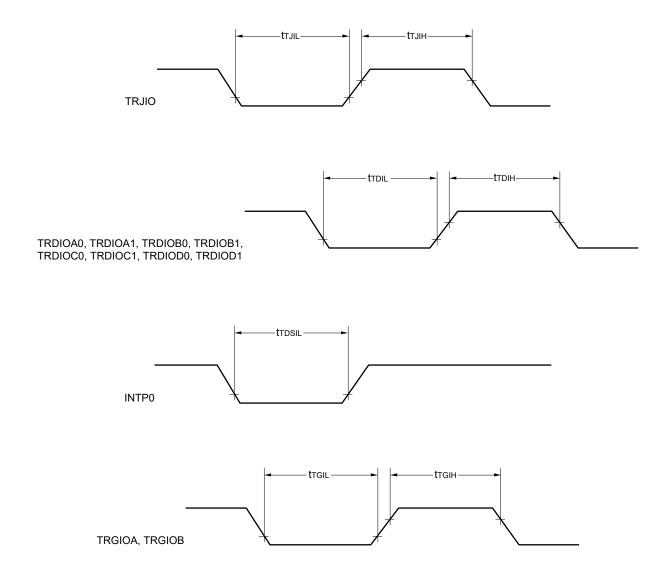
TI/TO Timing

TRDIOD0, TRDIOD1, TRGIOA, TRGIOB

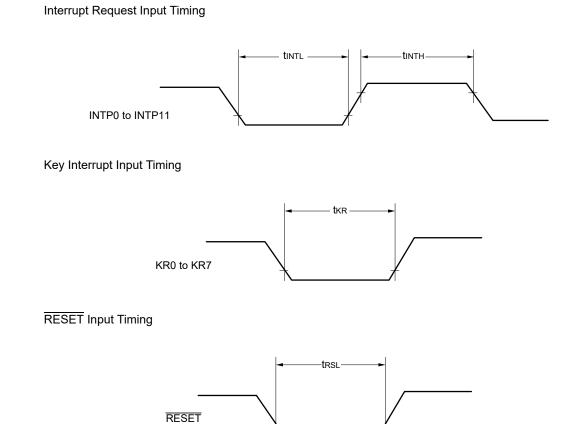








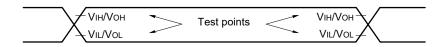






2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		$2.4~V \leq EV_{DD0} \leq 5.5~V$		fMCK/6 Note 2		fмск/6		fмск/6	bps
Note 1		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		$1.8 \text{ V} \leq EV\text{DD0} \leq 5.5 \text{ V}$		fMCK/6 Note 2		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		$1.7~V \leq EV_{DD0} \leq 5.5~V$		fмск/6 Note 2		fмск/6 Note 2		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		$1.6~V \leq EV_{DD0} \leq 5.5~V$		_		fмск/6 Note 2		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		_		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$: MAX. 2.6 Mbps

 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.4 \text{ V}$: MAX. 1.3 Mbps

 $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$: MAX. 0.6 Mbps

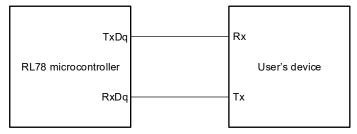
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:	32 MHz (2.7 V \leq VDD \leq 5.5 V)
	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq VDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

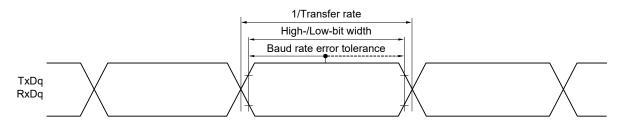
Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



RL78/G1F

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	C	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	$t_{KCY1} \geq 2/f_{CLK}$	$4.0~V \leq EV_{DD0} \leq 5.5~V$	62.5		250		500		ns
			$2.7~V \leq EV_{DD0} \leq 5.5~V$	83.3		250		500		ns
SCKp high-/low-level	tĸнı, tĸ∟ı	$4.0~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 - 7		tксү1/2 - 50		tксү1/2 - 50		ns
width		$2.7~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 - 1 0		tксү1/2 - 50		tксү1/2 - 50		ns
SIp setup time (to SCKp↑)	tsik1	$4.0~V \leq EV_{DD0} \leq 5.5~V$		23		110		110		ns
Note 1		$2.7~V \leq EV_{DD0} \leq 5.5~V$		33		110		110		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi1	$2.7~V \leq EV_{DD0} \leq 5.5~V$		10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 20 pF Note	4		10		10		10	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),

g: PIM and POM numbers (g = 1)

Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))



Parameter	Symbol	(Conditions	HS (high-s main) mo		LS (low-speed mode	d main)	LV (low-vol main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	$t_{KCY1} \geq 4/f_{CLK}$	$2.7~V \leq E_{VDD0} \leq 5.5~V$	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	250		500		1000		ns
			$1.8~V \leq EV_{DD0} \leq 5.5~V$	500		500		1000		ns
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	1000		1000		1000		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	_		1000		1000		ns
SCKp high-/low-level	tкнı,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns
width	tĸ∟ı	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 18		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 38		tксү1/2 - 50		tксү1/2 - 50		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	tксү1/2 - 1 00		tксү1/2 - 100		tксү1/2 - 100		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		_		tксү1/2 - 1 00		tксү1/2 - 1 00		ns
SIp setup time	tsıĸı	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		44		110		110		ns
(to SCKp↑) ^{Note 1}		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		44		110		110		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		75		110		110		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	110		110		110		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	220		220		220		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}}$	≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	$1.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	\leq 5.5 V	19		19		19		ns
(from SCKp↑) ^{Note 2}		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		_		19		19		ns
Delay time from SCKp↓ to SOp output _{Note 3}	tkso1	$\begin{array}{l} 1.7 \ V \leq EV_{DD0} \leq 5.5 \ V \\ C = 30 \ pF \ ^{Note \ 4} \end{array}$			25		25		25	ns
1000 5		$1.6 V \le EV_{DD0}$ C = 30 pF Note			—		25		25	ns

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



Parameter	Symbol	Cond	ditions	HS (high-spee mode	ed main)	LS (low-speed mode	d main)	LV (low-voltag mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tксү2	$4.0~V \leq EV_{DD0} \leq 5.5~V$	20 MHz < fмск	8/fмск		—		_		ns
time Note 5			fмск ≤ 20 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$	16 MHz < fмск	8/fмск		_		_		ns
			fмск ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	6/fмск and 750		6/fмск and 750		6/fмск and 750		ns	
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns	
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	—		6/fмск and 1500		6/fмск and 1500		ns	
SCKp high-/ tкн2,	,	$4.0~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		ns
low-level width	low-level width tkl2	$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$	tксү2/2 - 8		tксү2/2 - 8		tkcy2/2 - 8		ns	
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		ns
		$1.7~V \leq EV_{DD0} \leq 5.5~V$		tксү2/2 - 66		tксү2/2 - 66		tkcy2/2 - 66		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		—		tксү2/2 - 66		tkcy2/2 - 66		ns
SIp setup time	tsıĸ2	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns	
(to SCKp↑) _{Note 1}		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
		$1.7~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 40		1/fмск + 40		1/fмск + 40		ns	
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			1/fмск + 40		1/fмск + 40		ns
Slp hold time	tĸsı2	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
(from SCKp↑) Note 2		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		1/fмск + 250		1/fмск + 250		1/fмск + 250		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		—		1/fмск + 250		1/fмск + 250		ns
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 44		2/fмск + 110		2/fмск + 110	ns
SOp output Note 3			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		2/fмск + 75		2/fмск + 110		2/fмск + 110	ns
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 100		2/fмск + 110		2/fмск + 110	ns
			$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		2/fмск + 220		2/fмск + 220		2/fмск + 220	ns
			$1.6~V \le EV_{DD0} \le 5.5~V$		_		2/fмск + 220		2/fмск + 220	ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

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Remark 2. fMCK: Serial array unit operation clock frequency
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(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



(2/2)

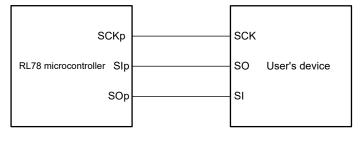
Parameter	Symbol		Conditions	HS (high-spee mode	d main)	LS (low-speed mode	l main)	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tssik	DAPmn = 0	$2.7~V \leq EV_{DD0} \leq 5.5~V$	120		120		120		ns
			$1.8~V \leq EV_{DD0} \leq 5.5~V$	200		200		200		ns
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	400		400		400		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	—		400		400		ns
		DAPmn = 1	$2.7~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	—		1/fмск + 400		1/fмск + 400		ns
SSI00 hold time	tĸssi	DAPmn = 0	$2.7~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	—		1/fмск + 400		1/fмск + 400		ns
		DAPmn = 1	$2.7~V \leq EV_{DD0} \leq 5.5~V$	120		120		120		ns
			$1.8~V \leq EV_{DD0} \leq 5.5~V$	200		200		200		ns
			$1.7~V \leq EV_{DD0} \leq 5.5~V$	400		400		400		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	—		400		400		ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

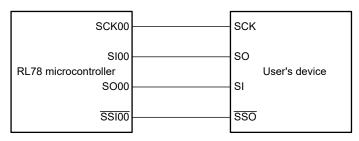
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)

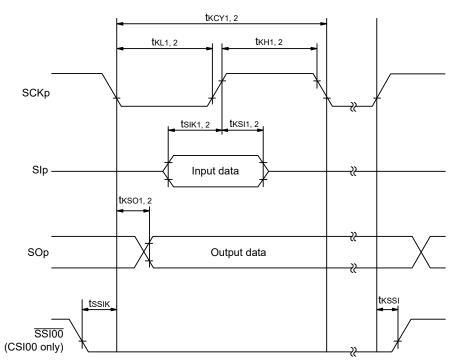


CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



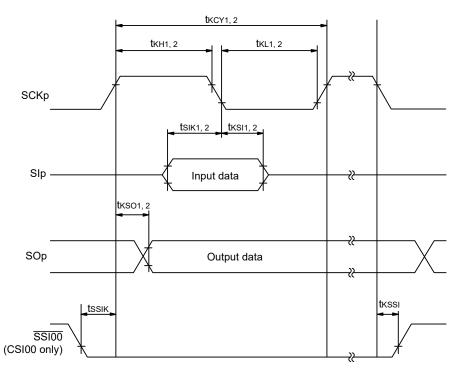
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)



Parameter	Symbol	Conditions		speed main) ode	-	peed main) ode		oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fsc∟	$\label{eq:constraint} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 50 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 2.7 k\Omega \end{array}$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$\label{eq:loss} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 3 k\Omega \end{array}$		400 Note 1		400 Note 1		400 Note 1	kHz
		$\label{eq:loss} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 k\Omega \end{array}$		300 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 k\Omega \end{array}$		250 Note 1		250 Note 1		250 Note 1	kHz
		$\label{eq:bound} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} \mbox{=} 5 k\Omega \end{array}$		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\label{eq:constraint} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF, } R_b = 2.7 \mbox{ k}\Omega \end{array}$	475		1150		1150		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} \mbox{=} 3 k\Omega \end{array}$	1150		1150		1150		ns
		$\label{eq:bound} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	1550		1550		1550		ns
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} \mbox{=} 5 k\Omega \end{array}$	1850		1850		1850		ns
		$\label{eq:bound} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} \mbox{=} 5 \mbox{ k}\Omega \end{array}$	_		1850		1850		ns
Hold time when SCLr = "H"	tніgн	$\label{eq:constraint} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 50 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 2.7 k\Omega \end{array}$	475		1150		1150		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 3 } k\Omega \end{array}$	1150		1150		1150		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	1550		1550		1550		ns
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	1850		1850		1850		ns
		$\label{eq:loss} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 k\Omega \end{array}$	_		1850		1850		ns

(5) During communication at same potential (simplified I²C mode)

(1/2)

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

Parameter	Symbol	Conditions	HS (high-speed r mode	main)	LS (low-speed n mode	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$\begin{array}{l} 2.7 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/fмск + 85 Note 2		1/f _{MCK} + 145 Note 2		1/fмск + 145 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ Rb} = 3 \mbox{ k}\Omega \end{array}$	1/fмск + 145 Note 2		1/f _{MCK} + 145 Note 2		1/fмск + 145 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF}, \mbox{ R}_b \mbox{ = 5 } \end{array}$	1/fмск + 230 Note 2		1/f _{MCK} + 230 Note 2		1/fMCK + 230 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	1/fмск + 290 Note 2		1/f _{MCK} + 290 Note 2		1/fMCK + 290 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	—		1/f _{MCK} + 290 Note 2		1/fmck + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$\begin{array}{l} 2.7 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 3 k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF}, \mbox{ R}_b \mbox{ = 5 } \kappa\Omega \end{array}$	_		0	405	0	405	ns

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

Note 1. The value must also be equal to or less than fMCK/4.

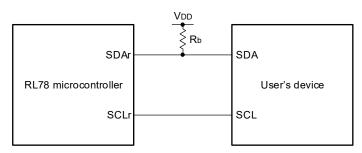
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

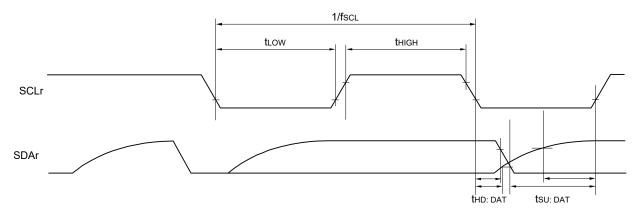
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remark 1.** $R_b[\Omega]$: Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1, 3, 5, 7),
- h: POM number (h = 0, 1, 3, 5, 7)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

Parameter	Symbol	Conditions			HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} N^{ote 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 4$		5.3		1.3		0.6	Mbps
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		5.3		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. Use it with $EV_{DD0} \ge V_b$.

Note 3.The following conditions are required for low voltage interface when EVDD0 < VDD. $2.4 V \le EVDD0 < 2.7 V$: MAX. 2.6 Mbps $1.8 V \le EVDD0 < 2.4 V$: MAX. 1.3 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:	32 MHz (2.7 V \leq VDD \leq 5.5 V)
	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq VDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)

Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

Parameter	Symbol		Conditions		-speed main) node		-speed main) mode	-	voltage main) node	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}\text{DD0} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

1

Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EVDD0 \ge Vb$.

Note 6. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

1

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times 100 [\%]}$$

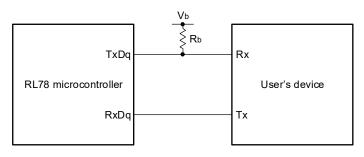
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 7.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

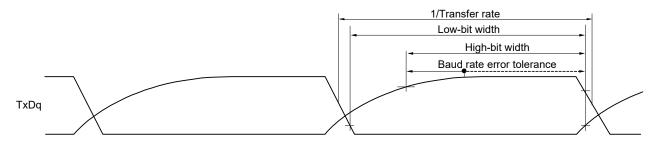
(Remarks are listed on the next page.)

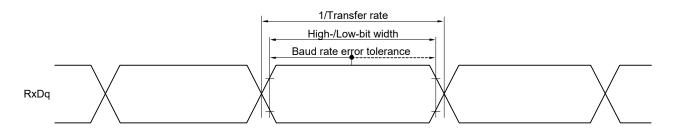


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remark 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-speed mode		LV (low-vo main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tκcγ1 ≥ 2/fc∟κ	$\begin{array}{l} 4.0 \; V \leq EV_{\text{DD0}} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	200		1150		1150		ns
			$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	300		1150		1150		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \; V \leq EV_{DDO} \\ 2.7 \; V \leq V_{b} \leq 4 \\ C_{b} = 20 \; pF, \; R_{b} \end{array}$	4.0 V,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 2 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	2.7 V,	tксү1/2 - 120		tксү1/2 - 120		tксү1/2 - 120		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \; V \leq EV_{DDO} \\ 2.7 \; V \leq V_{b} \leq V_{b} \\ C_{b} = 20 \; pF, \; R_{b} \end{array}$	4.0 V,	tксү1/2 - 7		tксү1/2 - 50		tксү1/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq \\ C_{b} \texttt{=} 20 \ pF, \ R_{b} \end{array}$	2.7 V,	tксү1/2 - 10		tксү1/2 - 50		tксү1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$\begin{array}{l} 4.0 \; V \leq EV_{DDO} \\ 2.7 \; V \leq V_{b} \leq V_{b} \\ C_{b} = 20 \; pF, \; R_{b} \end{array}$	4.0 V,	58		479		479		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 1 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$\begin{array}{l} 4.0 \; V \leq EV_{DDO} \\ 2.7 \; V \leq V_{b} \leq V_{b} \\ C_{b} = 20 \; pF, \; R_{b} \end{array}$	4.0 V,	10		10		10		ns
		$\begin{array}{l} 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 1 \\ \text{C}_{\text{b}} = 20 \text{ pF, R}_{\text{b}} \end{array}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp out- put ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \\ 2.7 \; V \leq V_{b} \leq \\ C_{b} = 20 \; pF, \; R_{b} \end{array}$	4.0 V,		60		60		60	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_{b} \leq 1 \\ C_{b} = 20 \ pF, \ R_{b} \end{array}$	2.7 V,		130		130		130	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(Notes, Caution, and Remarks are listed on the next page.)



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions	HS (high-sp mc		• •	oeed main) ode		ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı		23		110		110		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	33		110		110		ns
Slp hold time (from SCKp↓) ^{Note 2}	tksi1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	10		10		10		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	10		10		10		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		10		10		10	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		10		10		10	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/2)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 3. fMck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-spee mode		LV (low-vo main) mo	0	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1 ≥ 4/fclk		300		1150		1150		ns
			$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		1150		1150		ns
			$ \begin{split} & 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V \; ^{Note}, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $	1150		1150		1150		ns
SCKp high-level width	tкн1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \\ 2.7 \ V \leq V_b \leq 4 \\ C_b = 30 \ pF, \ R_b \end{array}$.0 V,	tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} \\ 2.3 \ V \leq V_b \leq 2. \\ C_b = 30 \ pF, \ R_b \end{array}$.7 V,	tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \\ 1.6 \ V \leq V_b \leq 2 \\ C_b = 30 \ pF, \ R_b \end{array}$.0 V ^{Note} ,	tксү1/2 - 45 8		tксү1/2 - 458		tксү1/2 - 458		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \\ 2.7 \ V \leq V_b \leq 4 \\ C_b = 30 \ pF, \ R_b \end{array}$.0 V,	tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns
		$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \\ 2.3 \ \text{V} \leq \text{V}_{\text{b}} \leq 2 \\ \text{C}_{\text{b}} = 30 \ \text{pF}, \ \text{R}_{\text{b}} \end{array}$.7 V,	tксү1/2 - 18		tксү1/2 - 50		tксү1/2 - 50		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \\ 1.6 \ V \leq V_b \leq 2 \\ C_b = 30 \ pF, \ R_b \end{array}$	0 V ^{Note} ,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/3)

Note Use it with $EV_{DD0} \ge V_b$.

(Remarks are listed two pages after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		speed main) ode	•	peed main) ode	`	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı		81		479		479		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	177		479		479		ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2,} \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $	479		479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tκsıı		19		19		19		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	19		19		19		ns
		$\label{eq:linear} \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	19		19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1			100		100		100	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		195		195		195	ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $		483		483		483	ns

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/3)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

 $\label{eq:Note 2.} \textbf{Note 2.} \qquad \textbf{Use it with } EV_{DD0} \geq V_b.$

(**Remarks** are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		speed main) ode	•	peed main) ode	•	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 1}	tsıĸı		44		110		110		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	44		110		110		ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_{b} \leq 2.0 \ V \ Note \ 2, \\ & C_{b} = 30 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split} $	110		110		110		ns
SIp hold time (from SCKp↓) ^{Note 1}	tκsıı		19		19		19		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	19		19		19		ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2,} \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $	19		19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		25		25		25	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		25		25		25	ns
		$ \begin{split} & 1.8 \ \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \ \text{V} \ ^{\text{Note 2}}, \\ & \text{C}_{\text{b}} = 30 \ \text{pF}, \ \text{R}_{\text{b}} = 5.5 \ \text{k}\Omega \end{split} $		25		25		25	ns

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(3/3)

Note 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

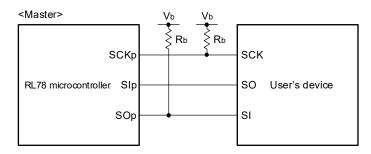
 $\label{eq:Note 2.} \textbf{Note 2.} \qquad \textbf{Use it with } \textbf{EV} \textbf{DD} \textbf{0} \geq \textbf{V} \textbf{b}.$

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)



CSI mode connection diagram (during communication at different potential)



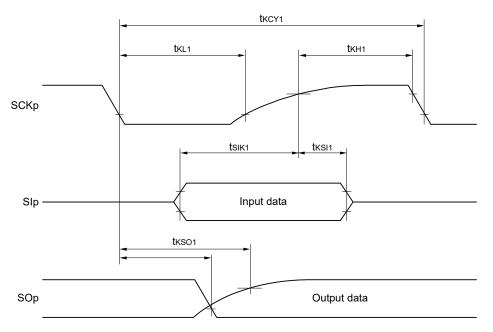
Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

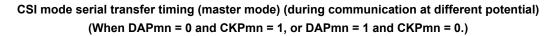
Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

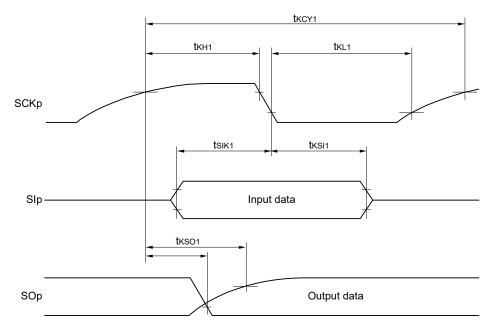
Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- **Remark 1.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Cor		h-speed mode		/-speed mode		-voltage mode	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү2	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V,$	24 MHz < fмск	14/fмск		—		—		ns
Note 1		$2.7~V \leq V_b \leq 4.0~V$	$20 \text{ MHz} < \text{fmck} \le 24 \text{ MHz}$	12/fмск		—		—		ns
			$8 \text{ MHz} < \text{fmck} \le 20 \text{ MHz}$	10/fмск		—		—		ns
			$4 \text{ MHz} < fMCK \le 8 \text{ MHz}$	8/fмск		16/fмск		—		ns
			fмск \leq 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$2.7~V \leq EV_{\text{DD0}} < 4.0~V,$	24 MHz < fмск	20/fмск		—		—		ns
		$2.3~V \leq V_b \leq 2.7~V$	$20 \text{ MHz} < \text{fmck} \le 24 \text{ MHz}$	16/fмск		—		—		ns
			$16 \; MHz < f_{MCK} \leq 20 \; MHz$	14/fмск		—		—		ns
			$8 \text{ MHz} < \text{fmck} \le 16 \text{ MHz}$	12/fмск		—		—		ns
	4 M		$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	8/fмск		16/fмск		—		ns
			fмск \leq 4 MHz	6/fмск		10/fмск		10/fмск		ns
		$1.8 \ V \leq EV \text{dd} < 3.3 \ V,$	24 MHz < fмск	48/fмск		—		—		ns
		$1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2	$20 \text{ MHz} < \text{fmck} \leq 24 \text{ MHz}$	36/fмск		—		—		ns
		Note 2	$16 \text{ MHz} < \text{fmck} \le 20 \text{ MHz}$	32/fмск		_		—		ns
			$8 \text{ MHz} < \text{fmck} \le 16 \text{ MHz}$	26/fмск		—		—		ns
			$4 \text{ MHz} < f_{MCK} \leq 8 \text{ MHz}$	16/fмск		16/fмск		—		ns
			fмск \leq 4 MHz	10/fмск		10/fмск		10/fмск		ns
SCKp high-/	tкн2,	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2$	$2.7~V \leq V_b \leq 4.0~V$	tксү2/2		tkcy2/2		tксү2/2		ns
low-level width	tĸ∟2			- 12		- 50		- 50		
		$2.7~V \leq EV_{DD0} < 4.0~V, 2$	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 - 18		tксү2/2 - 50		tксү2/2 - 50		ns
		$1.8~V \leq EV_{DD0} < 3.3~V,~T$	$1.6~V \leq V_b \leq 2.0~V$ Note 2	tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsık2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2$	$2.7~V \leq V_b \leq 4.0~V$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 4.0 \text{ V}, 2$	$2.3~V \leq V_b \leq 2.7~V$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.3 \text{ V}, $	$1.6~V \leq V_b \leq 2.0~V~\text{Note}~2$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) _{Note 4}	tksı2			1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp	tĸso2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \ 2\\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$			2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
output Note 5		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$			2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ C_b = 30 \ pF, \ R_v = 5.5 \ k\Omega \end{array}$	1.6 V \leq Vb \leq 2.0 V Note 2,		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

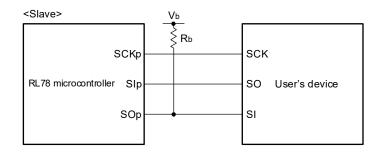
(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(Notes, Cautions, and Remarks are listed on the next page.)



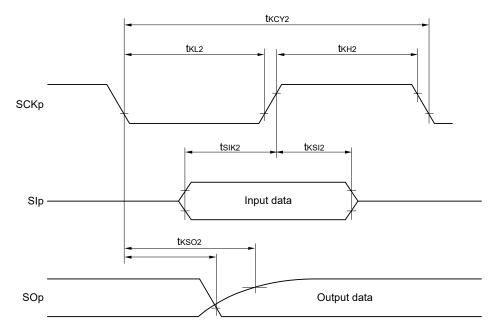
- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD0 \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

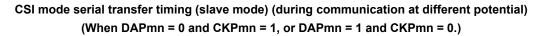


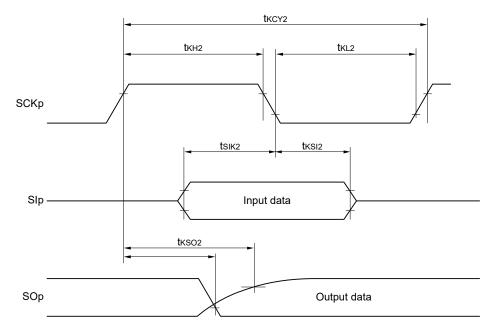
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified l²C mode) (TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		speed main) 10de	-	speed main) node	`	oltage main) 10de	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fsc∟			1000 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		1000 Note 1		300 Note 1		300 Note 1	kHz
				400 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:Volume} \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ & C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t∟ow		475		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	475		1550		1550		ns
			1150		1550		1550		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1150		1550		1550		ns
		$\label{eq:linear} \begin{split} & 1.8 \ \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_b \leq 2.0 \ \text{V}^{\text{Note 2}}, \\ & \text{C}_b = 100 \ \text{pF}, \ \text{R}_b = 5.5 \ \text{k}\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	thigh		245		610		610		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	200		610		610		ns
			675		610		610		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	600		610		610		ns
		$\label{eq:VD0} \begin{split} & 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V \; \text{Note 2}, \\ & C_b = 100 \; \text{pF}, \; R_b = 5.5 \; \text{k}\Omega \end{split}$	610		610		610		ns

(2/2)

Conditions HS (high-speed main) Unit Parameter Symbol LS (low-speed main) LV (low-voltage main) mode mode mode MIN. MAX. MIN. MAX. MIN. MAX. Data setup time tsu:dat $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 1/fмск + 135 Note 3 1/fmck + 190 Note 3 1/fмск + 190 Note 3 ns (reception) $27 V \le V_{b} \le 40 V$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ 1/fмск + 135 Note 3 1/fmck + 190 Note 3 1/fмск + 190 Note 3 ns $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 1/fmck + 190 Note 3 1/fmck + 190 Note 3 1/fмск + 190 Note 3 ns $2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega$ $2.7 V \le EV_{DD0} < 4.0 V.$ 1/fмск + 190 Note 3 1/fmck + 190 Note 3 1/fmck + 190 Note 3 ns $2.3~V \leq V_b \leq 2.7~V,$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}.$ 1/fmck + 190 Note 3 1/fmck + 190 Note 3 1/fmck + 190 Note 3 ns $1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$ Note 2, $C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ Data hold time $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ 0 305 0 305 0 305 thd:dat ns (transmission) $27 V \le V_{b} \le 40 V$ $C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$ $2.7 V \le EV_{DD0} < 4.0 V$, 0 305 0 305 0 305 ns $2.3 V < V_b < 2.7 V_c$ C_b = 50 pF, R_b = 2.7 k Ω $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 0 355 0 355 0 355 ns $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega$ $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ 0 355 0 355 0 355 ns $2.3~V \leq V_b \leq 2.7~V,$ C_b = 100 pF, R_b = 2.7 k Ω $1.8 V \le EV_{DD0} < 3.3 V$, 0 405 0 405 0 405 ns 1.6 V \leq Vb \leq 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 k Ω

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified l²C mode) (TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Note 1. The value must also be equal to or less than fMCK/4.

Note 2. Use it with $EVDD0 \ge Vb$.

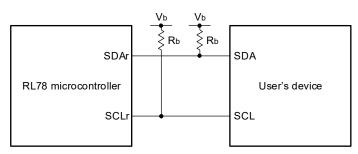
Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

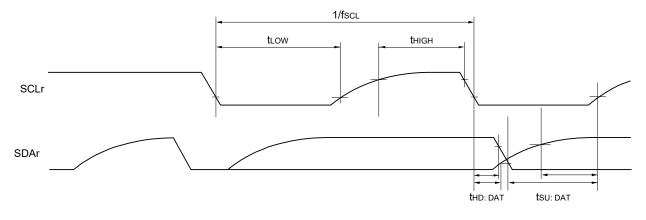
(Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01, 10, 11, 20), g: PIM, POM number (g = 0, 1, 3, 5, 7)
- **Remark 3.** fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)



2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 $~\leq$ VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Conditions			peed main) ode	· ·	beed main) bde		ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
frequency		fclk ≥ 1 MHz	$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
			$1.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
			$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$	-	_	0	100	0	100	kHz
Setup time of	tsu: sta	$2.7 \text{ V} \leq EV_{DD0} \leq 3$	5.5 V	4.7		4.7		4.7		μs
restart condition		$1.8 V \le EV_{DD0} \le 8$	5.5 V	4.7		4.7		4.7		μs
		$1.7 V \le EV_{DD0} \le 8$	5.5 V	4.7		4.7		4.7		μs
		$1.6 V \le EV_{DD0} \le 8$	5.5 V	-	_	4.7		4.7		μs
Hold time Note 1	thd: STA	$2.7 V \le EV_{DD0} \le 3$	5.5 V	4.0		4.0		4.0		μs
		$1.8 V \le EV_{DD0} \le 8$	5.5 V	4.0		4.0		4.0		μs
		$1.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.6 V \le EV_{DD0} \le 8$	5.5 V	-	_	4.0		4.0		μs
Hold time when	tLOW	$2.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		$1.8 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.7		4.7		4.7		μs
		$1.7 V \le EV_{DD0} \le 8$	5.5 V	4.7		4.7		4.7		μs
		$1.6 V \le EV_{DD0} \le 8$	5.5 V	-	_	4.7		4.7		μs
Hold time when	tніgн	$2.7 V \le EV_{DD0} \le 8$	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		$1.8 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.6 V \le EV_{DD0} \le 8$	5.5 V	-	_	4.0		4.0		μs

 $(\ensuremath{\textit{Notes}}, \ensuremath{\textit{Caution}}, \ensuremath{\textit{and}} \ensuremath{\textit{Remark}}$ are listed on the next page.)



(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)

Parameter	Symbol	Conditions		peed main) ode		beed main) bde		oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq 5.5~V$	250		250		250		ns
		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		250		250		ns
		$1.7~V \leq EV_{DD0} \leq 5.5~V$	250		250		250		ns
		$1.6~V \leq EV_{DD0} \leq 5.5~V$	-	_	250		250		ns
Data hold time (transmission)	thd: dat	$2.7~V \leq EV_{DD0} \leq 5.5~V$	0	3.45	0	3.45	0	3.45	μs
Note 2		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	3.45	0	3.45	0	3.45	μs
		$1.7~V \leq EV_{DD0} \leq 5.5~V$	0	3.45	0	3.45	0	3.45	μs
		$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$	-		0	3.45	0	3.45	μs
Setup time of stop condition	tsu: sto	$2.7~V \leq EV_{DD0} \leq 5.5~V$	4.0		4.0		4.0		μs
		$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$	4.0		4.0		4.0		μs
		$1.7~V \leq EV_{DD0} \leq 5.5~V$	4.0		4.0		4.0		μs
		$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$	-		4.0		4.0		μs
Bus-free time	t BUF	$2.7~V \leq EV_{DD0} \leq 5.5~V$	4.7		4.7		4.7		μs
		$1.8~V \leq EV_{DD0} \leq 5.5~V$	4.7		4.7		4.7	1	μs
		$1.7~V \leq EV_{DD0} \leq 5.5~V$	4.7		4.7		4.7		μs
		$1.6~V \leq EV_{DD0} \leq 5.5~V$	-	<u> </u>	4.7	Ī	4.7	1	μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of tHD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: Cb = 400 pF, Rb = 2.7 k Ω



(2) I²C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	rmbol Conditions			h-speed mode		/-speed mode		-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \leq EV_{DD0} \leq 5.5~V$	0	400	0	400	0	400	kHz
		fc∟k ≥ 3.5 MHz	$1.8~V \le EV_{DD0} \le 5.5~V$	0	400	0	400	0	400	kHz
Setup time of restart condi-	tsu: sta	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
tion		$1.8~V \leq EV_{DD0} \leq$	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			0.6		0.6		μs
Hold time Note 1	thd: STA	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq$	5.5 V	1.3		1.3		1.3		μs
		$1.8~V \leq EV_{DD0} \leq$	5.5 V	1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	tніgн	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
		$1.8~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq$	5.5 V	100		100		100		ns
		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	100		100		100		ns
Data hold time (transmission)	thd: dat	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0	0.9	0	0.9	0	0.9	μs
Note 2		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
		$1.8~V \leq EV_{DD0} \leq$	$1.8 \ V \leq EV_{DD0} \leq 5.5 \ V$			0.6		0.6		μs
Bus-free time	t BUF	$2.7~V \leq EV_{DD0} \leq$	5.5 V	1.3		1.3		1.3		μs
		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of tHD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω



(3) I²C fast mode plus

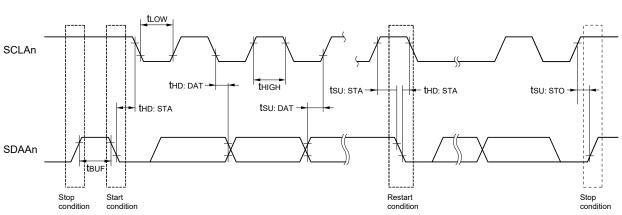
(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Co	onditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
					MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode plus: fc∟ĸ ≥ 10 MHz	$2.7~V \leq EV_{DD0} \leq 5.5~V$	0	1000	-	_	-	_	kHz
Setup time of restart condi- tion	tsu: sta	$2.7 \text{ V} \leq EV_{DD0} \leq 5.7$.5 V	0.26		-	_	-	_	μs
Hold time Note 1	thd: STA	$2.7~V \leq EV_{DD0} \leq 5.4$.5 V	0.26		-	_	-	_	μs
Hold time when SCLA0 = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.4$.5 V	0.5		-	_	-	_	μs
Hold time when SCLA0 = "H"	tніgн	$2.7 \text{ V} \leq EV_{DD0} \leq 5.7$.5 V	0.26		-	_	-	_	μs
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq 5.4$.5 V	50		-	_	-	_	ns
Data hold time (transmission) Note 2	thd: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.7 \text{ V}$.5 V	0	0.45	-	_	-	_	μs
Setup time of stop condition	tsu: sto	$2.7~V \leq EV_{DD0} \leq 5.4$.5 V	0.26		-	_	-	_	μs
Bus-free time	t BUF	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		0.5		-	_	-	_	μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of the DEDAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- RemarkThe maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at
that time in each mode are as follows.
Fast mode plus: Cb = 120 pF, Rb = 1.1 k Ω



IICA serial transfer timing

Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI7	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI24	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$		1.2	±3.5	LSB
		AVREFP = VDD Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V~^{Note~4}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \le V_{DD} \le 5.5~V$	17		39	μS
			$1.6~V \le V_{DD} \le 5.5~V$	57		95	μS
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
			$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μS
			$2.4~V \le V \text{dd} \le 5.5~V$	17		39	μS
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±0.25	%FSR
		AV _{REFP} = V _{DD} Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V~^{Note~4}$			±0.50	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			39 95 39 39 39 39 ±0.25	%FSR
		AV _{REFP} = V _{DD} Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$ Note 4	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	%FSR		
Integral linearity error Note 1	ILE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$		1.2 ±7.0 25 39 875 39 7 95 7 95 75 39 625 39 7 25 95 39 625 39 7 ±0.25 ±0.25 ±0.50 ±0.50 ±0.50 ±0.50 ±2.5 ±5.0 ±1.5 ±1.5 ±2.0 0 AVREFP VBGR Note 5 VBGR Note 5	LSB	
		AVREFP = VDD Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			LSB	
Differential linearity error Note 1	DLE	DLE 10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±1.5	LSB
		AVREFP = VDD Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$ Note 4			±2.0	LSB
Analog input voltage	Vain	ANI2 to ANI7		0		AVREFP	V
		Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 5		V	
		Temperature sensor output voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed m			te 5	V	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3.	When AVREFP < VDD, the MAX. values are as follows.						
	Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.					
	Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.					
	Integral linearity error/ Differential linearity error:	Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.					
Note 4.	Values when the conversion time is set to 57 μs	(min.) and 95 μs (max.).					

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI24

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage
(+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8~V \le AV_{\text{REFP}} \le 5.5~V$		1.2	±5.0	LSB
		$EVDD0 \le AVREFP = VDD$ Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V~Note~5$		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution Target ANI pin: ANI16 to ANI24	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V~\text{Note}~5$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8~V \le AV_{\text{REFP}} \le 5.5~V$			±0.35	%FSR
		$EV_{DD0} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V~^{Note~5}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8~V \le AV_{\text{REFP}} \le 5.5~V$			±3.5	LSB
		$EV_{DD0} \le AV_{REFP} = V_{DD} \text{ Notes 3, 4}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V~\text{Note}~5$			±6.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \le AV_{\text{REFP}} \le 5.5~V$			±2.0	LSB
		$EV_{DD0} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V~Note~5$			±2.5	LSB
Analog input voltage	Vain	ANI16 to ANI24		0		AVREFP and EVDD0	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD0 \le AVREFP \le VDD$, the MAX. values are as follows.

 Overall error:
 Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

 Zero-scale error/Full-scale error:
 Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

 Integral linearity error/ Differential linearity error:
 Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

 Note 4.
 When AVREFP < EVDD0 ≤ VDD, the MAX. values are as follows.</td>

 Overall error:
 Add ±4.0 LSB to the MAX. value when AVREFP = VDD.

 Zero-scale error/Full-scale error:
 Add ±0.20%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

Note 5. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI17, ANI16 to ANI24, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8~V \leq V \text{DD} \leq 5.5~V$		1.2	±7.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V~Note~3$		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution Target pin: ANI0 to ANI7, ANI16 to ANI24	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs		±0.60	%FSR			
			$1.6~V \leq V_{DD} \leq 5.5~V~Note~3$			±0.85	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V~Note~3$			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V~\text{Note}~3$			±6.5	LSB
Differential linearity error DLE		10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Note 1			$1.6~V \leq V_{DD} \leq 5.5~V~\text{Note}~3$			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI7		0		Vdd	V
		ANI16 to ANI24				EV _{DD0}	V
		Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			V _{TMPS25} Note 4		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI7, ANI16 to ANI24

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD0 \leq VDD, Vss = EVss0 = 0 V, Reference voltage (+) = VBGR ^{Note 3}, Reference voltage (-) = AVREFM = 0 V ^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	tCONV	8-bit resolution	$2.4~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN		•	0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



RL78/G1F

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = EVsso = 0 V, HS (high-speed main) mode)

2.6.3 D/A converter characteristics

(TA = -40 to +85°C, 1.6 V \leq EVsso \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 M Ω	$1.8~V \leq V\text{dd} \leq 5.5~V$			±2.5	LSB
		Rload = 8 M Ω	$1.8~V \leq V\text{dd} \leq 5.5~V$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7~V \leq V\text{DD} \leq 5.5~V$			3	μs
			$1.6~V \leq V_{DD} < 2.7~V$			6	μs



2.6.4 Comparator

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP				±5	±40	mV
Input voltage range	VICMP			0		Vdd	V
Internal reference	ΔV_{IREF}	CmRVM register value : 7	CmRVM register value : 7FH to 80H (m = 0, 1)			±2	LSB
voltage deviation		Other than above				±1	LSB
Response Time	tcr, tcr	Input amplitude±100mV			70	150	ns
Operation stabilization	tсмр	CMPn = 0→1	V _{DD} = 3.3 to 5.5 V			1	μs
time ^{Note 1}			V _{DD} = 2.7 to 3.3 V			3	μs
Reference voltage stabilization wait time	tvr	$CVRE: 0 \rightarrow 1^{Note 2}$				20	μs
Operation current	ICMPDD	Separately, it is defined as	the operation current of perip	heral function	ons.		

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. Time taken until the comparator satisfies the DC/AC characteristics after the comparator operation enable signal is switched (CMPnEN = $0 \rightarrow 1$).

Note 2. Enable comparator output (CnOE bit = 1; n = 0 to 1) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 1) and waiting for the operation stabilization time to elapse.

2.6.5 PGA

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	Vipga			0		0.9 × V _{DD} / Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{\text{DD}}$			V
	VIOLPGA					$0.07\times V_{\text{DD}}$	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32				±2	%
Slew rate	SRrpga	 Rising When Vin= 0.1Vpb/gain to 0.9Vpb/gain. 10 to 90% of output voltage amplitude 	$4.0 V \le V_{DD} \le 5.5 V$ (Other than x32)	3.5			V/µs
			$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
	SRFPGA	Falling When Vin= 0.1Vpb/gain to 0.9Vpb/gain.	$4.0 V \le V_{DD} \le 5.5 V$ (Other than x32)	3.5			
		90 to 10% of output	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time- Note 1	X10, X32					10	μs
Operation current	IPGADD	Separately, it is defined a	as the operation current of per	ripheral function	ons.	•	

Note 1. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

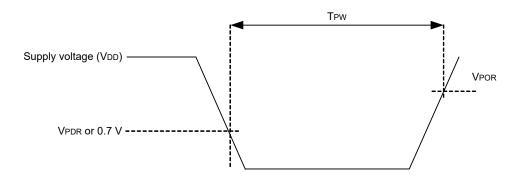
2.6.6 POR circuit characteristics

(T۵	=	-40	to	+85	2	Vss	= 0	V)
۰.	IA	_	-40	ω	.03	υ,	v 33	- 0	v)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	POR Voltage threshold on VDD rising		1.51	1.55	V
	VPDR	Voltage threshold on VDD falling Note 1	1.46	1.50	1.54	V
Minimum pulse width Note 2	TPW		300			μs

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in **2.4 AC Characteristics**.

Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPDR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.7 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

	Parameter		Conditions	MIN.	TYP.	MAX.	Unit
Voltage	Supply voltage level	VLVD0	Rising edge	3.98	4.06	4.14	V
detection			Falling edge	3.90	3.98	4.06	V
threshold		VLVD1	Rising edge	3.68	3.75	3.82	V
			Falling edge	3.60	3.67	3.74	V
		VLVD2	Rising edge	3.07	3.13	3.19	V
			Falling edge	3.00	3.06	3.12	V
		VLVD3	Rising edge	2.96	3.02	3.08	V
			Falling edge	2.90	2.96	3.02	V
		VLVD4	Rising edge	2.86	2.92	2.97	V
			Falling edge	2.80	2.86	2.91	V
		VLVD5	Rising edge	2.76	2.81	2.87	V
			Falling edge	2.70	2.75	2.81	V
		VLVD6	Rising edge	2.66	2.71	2.76	V
			Falling edge	2.60	2.65	2.70	V
		VLVD7	Rising edge	2.56	2.61	2.66	V
			Falling edge	2.50	2.55	2.60	V
		VLVD8	Rising edge	2.45	2.50	2.55	V
			Falling edge	2.40	2.45	2.50	V
		VLVD9	Rising edge	2.05	2.09	2.13	V
			Falling edge	2.00	2.04	2.08	V
		VLVD10	Rising edge	1.94	1.98	2.02	V
			Falling edge	1.90	1.94	1.98	V
		VLVD11	Rising edge	1.84	1.88	1.91	V
			Falling edge	1.80	1.84	1.87	V
		VLVD12	Rising edge	1.74	1.77	1.81	V
			Falling edge	1.70	1.73	1.77	V
		VLVD13	Rising edge	1.64	1.67	1.70	V
			Falling edge	1.60	1.63	1.66	V
Minimum pu	lse width	tLw		300			μs
Detection de	lay time					300	μs



(2) Interrupt & Reset Mode

Parameter	Symbol		Cor	MIN.	TYP.	MAX.	Unit	
Voltage detection	VLVDA0	VPOC2,	, VPOC1, VPOC0 = 0, 0, 0, f	alling reset voltage	1.60	1.63	1.66	V
threshold	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	Vlvda3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC2,	, VPOC1, VPOC0 = 0, 0, 1, f	alling reset voltage	1.80	1.84	1.87	V
	VLVDB1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	Vlvdb3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC2,	, VPOC1, VPOC0 = 0, 1, 0, f	alling reset voltage	2.40	2.45	2.50	V
	VLVDC1	ĺ	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2,	, VPOC1, VPOC0 = 0, 1, 1, f	alling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	Vlvdd2	1	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	Vlvdd3	1	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.8 Power supply voltage rising slope characteristics

(TA = -40 to +85°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.



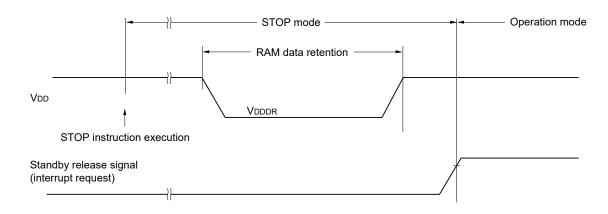
2.7 RAM Data Retention Characteristics

(TA = -40 to	+85°C,	Vss = 0V))
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	Vdddr		1.46 Notes 1, 2		5.5	V

Note 1. The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



2.8 Flash Memory Programming Characteristics

		,					
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$1.8 \ V \leq V_{DD} \leq 5.5 \ V$		1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	TA = 85°C	10,000			

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

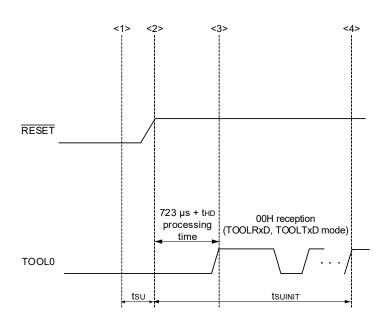
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming			1,000,000	bps



2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} < \text{EV}_{DD0} < \text{V}_{DD} < 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	ts∪	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thd	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu:How long from when the TOOL0 pin is placed at the low level until a pin reset ends

 $\ensuremath{\mathsf{tHD}}\xspace$ HD:How long to keep the TOOL0 pin at the low level from when the external resets end

(excluding the processing time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F11BxxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, or EVss0 pin, replace EVDD0 with VDD, or replace EVss0 with Vss.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G1F User's Manual.
- Caution 4. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- **Remark** When the products "G: Industrial applications" is used in the range of $T_A = -40$ to $+85^{\circ}C$, see 2. **ELECTRICAL SPECIFICATIONS (TA = -40 to +85^{\circ}C)**.



Operation of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above
85°C differs from that of products rated "A: Consumer applications" in the ways listed below.

Parameter	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	$\begin{array}{l} \text{HS (high-speed main) mode:} \\ 2.7 \ \text{V} \leq \ \text{Vdd} \leq 5.5 \ \text{V@1 MHz to } 32 \ \text{MHz} \\ 2.4 \ \text{V} \leq \ \text{Vdd} \leq 5.5 \ \text{V@1 MHz to } 16 \ \text{MHz} \\ \text{LS (low-speed main) mode:} \\ 1.8 \ \text{V} \leq \ \text{Vdd} \leq 5.5 \ \text{V@1 MHz to } 8 \ \text{MHz} \\ \text{LV (low-voltage main) mode:} \\ 2.4 \ \text{V} \leq \ \text{Vdd} \leq 5.5 \ \text{V@1 MHz to } 4 \ \text{MHz} \\ \end{array}$	HS (high-speed main) mode only: 2.7 V \leq VDD \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	$\begin{array}{l} 1.8 \ V \leq V \text{DD} \leq 5.5 \ V; \\ \pm 1.0\% \ @ \ T \text{A} = -20 \ \text{to} + 85^{\circ}\text{C} \\ \pm 1.5\% \ @ \ T \text{A} = -40 \ \text{to} -20^{\circ}\text{C} \\ 2.4 \ V \leq V \text{DD} < 1.8 \ V; \\ \pm 5.0\% \ @ \ T \text{A} = -20 \ \text{to} + 85^{\circ}\text{C} \\ \pm 5.5\% \ @ \ T \text{A} = -40 \ \text{to} -20^{\circ}\text{C} \end{array}$	2.4 V \leq VDD \leq 5.5 V: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART CSI: fcLk/2 (16 Mbps supported), fcLk/4 Simplified I ² C communication	UART CSI: fcLk/4 Simplified I ² C communication
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage detector	 Rising: 1.67 V to 4.06 V (14 stages) Falling: 1.63 V to 3.98 V (14 stages) 	• Rising: 2.61 V to 4.06 V (8 stages) • Falling: 2.55 V to 3.98 V (8 stages)

Remark The electrical characteristics of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differ from those of products "A: Consumer applications". For details, refer to **3.1** to **3.10**.



(1/2)

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD0		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V _{DD} +0.3 ^{Note 1}	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	P20 to P27, P121 to P124, P137, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 Note 2	V
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 Note 2	V
	Vo2	P20 to P27	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI24	-0.3 to EVDD0 +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	Vai2	ANI0 to ANI7	-0.3 to VDD +0.3 and -0.3 to AVREF(+) +0.3 Notes 2, 3	V

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage



Absolute Maximum Ratings

(2/2)

	anngo				(2)
Parameter	Symbols		Conditions	Ratings	Unit
Output current, high IOH1		Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147	-40	mA
		Total of all	P00 to P04, P40 to P43,P120, P130, P140, P141	-70	mA
		pins -170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40-P43, P50 to P55, P60 to P63, P70 to P77, P120, P130, P140, P141, P146, P147	40	mA
		Total of all	P00 to P04, P40 to P47, P120, P130, P140, P141	70	mA
		pins 170 mA	P05, P06, P10 to P17, P30, P31, P50 to P55, P70 to P77, P146, P147	100	mA
	IOL2	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient tem-	Та	In normal operation mode		-40 to +105	°C
perature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.



3.2 Oscillator Characteristics

3.2.1 X1, XT1 characteristics

(TA = -40 to +105°C, 2.4 V \leq EV_{DD0} = VDD \leq 5.5 V, Vss = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V \text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \le \text{V}_{\text{DD}}$ < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq EV_{DD0} = VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fін	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1		32	MHz
Notes 1, 2		$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$	1		16	MHz
High-speed on-chip oscillator clock frequency		T _A = +85 to +105°C	-2		2	%
accuracy		T _A = -20 to +85°C	-1		1	%
		T _A = -40 to -20°C	-1.5		1.5	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1F User's Manual.

3.3 DC Characteristics

3.3.1 Pin characteristics

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	put current, high ^{Note 1} IOH1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P55, P70 to P77, P120, P130, P140, P141, P146, P147				-3.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-30.0	mA
		(When duty $< 70\%$ Note 3)	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			-10.0	mA
			$2.4~V \leq EV_{DD0} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV \text{dd} \leq 5.5~V$			-30.0	mA
		P30, P31, P50 to P53,	$2.7 \text{ V} \leq EV_{DD0} < 4.0 \text{ V}$			-19.0	mA
		P70 to P77, P146, P147 (When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 2.7 \text{ V}$			-10.0	mA
Ior		Total of all pins (When duty ≤ 70% ^{Note 3})				-60.0	mA
	Іон2	IOH2 Per pin for P20 to P27				-0.1 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$2.4~V \leq V \text{DD} \leq 5.5~V$			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, VDD pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IOH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77,P120, P130, P140, P141, P146, P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P43,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P120, P130, P140, P141	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
		(When duty \leq 70% ^{Note 3})	$2.4~V \leq EV_{DD0} < 1.8~V$			9.0	mA
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV \text{DD0} \leq 5.5~V$			40.0	mA
		P30, P31, P50 to P55, P60 to	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P63, P70 to P77, P146, P147 (When duty \leq 70% ^{Note 3})	$2.4~V \leq EV_{DD0} < 1.8~V$			20.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				80.0	mA
	IOL2	Per pin for P20 to P27				0.4 Note 2	mA
		Total of all pins (When duty \leq 70% ^{Note 3})	$2.4~V \le V \text{DD} \le 5.5~V$			5.0	mA

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(2/5)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso and Vss pins.

Note 2. Do not exceed the total current value.

 Note 3.
 Specification under conditions where the duty factor ≤ 70%.

 The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOL \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	Normal input buffer	0.8 EVDD0		EVDD0	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	2.2		EVDD0	V
			TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} \le 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer 2.4 V \leq EVDD0 < 3.3 V	1.5		EVDD0	V
	Vінз	P20 to P27 (when P20 is used as	a port pin)	0.7 Vdd		Vdd	V
	VIH4	P60 to P63		0.7 EVDD0		6.0	V
	Vih5	P121 to P123, P137, EXCLK, EX P20 is used as INTP11 pin)	0.8 Vdd		Vdd	V	
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, Normal input buffer P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147 P147		0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P50, P53 to P55,	TTL input buffer $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \le \text{EV}_{\text{DD0}} \le 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V \leq EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27 (when P20 is used as	a port pin)	0		0.3 Vdd	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	Vil5	P121 to P124, P137, EXCLK, EX P20 is used as INTP11 pin)	0		0.2 Vdd	V	

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(3/5)

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 is EVDD0, even in the N-ch open-drain mode.



Items	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Output voltage, high	Voh1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OH1} = -3.0 \ mA \end{array}$	EVDD0 - 0.7			V
		P70 to P77, P120, P130, P140, P141, P146, P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -2.0 mA	EVDD0 - 0.6			V
			2.4 V ≤ EVDD0 < 5.5 V, Іон1 = -1.5 mA	EVDD0 - 0.5			V
	Vон2	P20 to P27	2.4 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA	Vdd - 0.5			V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ I_{OL1} = 8.5 \ mA \end{array}$			0.7	V
		P70 to P77, P120, P130, P140, P141, P146, P147	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \\ \text{IOL1} = 3.0 \ \text{mA} \end{array}$			0.6	V
			$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{I}_{\text{OL1}} = 1.5 \ \text{mA} \end{array}$			0.4	V
			$\begin{array}{l} 2.4 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{I}_{\text{OL1}} = 0.6 \ \text{mA} \end{array}$			0.4	V
	Vol2	P20 to P27	$\begin{array}{l} 2.4 \ V \leq V \text{DD} \leq 5.5 \ V, \\ \text{Iol2} = 400 \ \mu A \end{array} \end{array}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 15.0 mA			2.0	V
			$\begin{array}{l} 4.0 \ \text{V} \leq \text{EV} \text{DD0} \leq 5.5 \ \text{V}, \\ \text{IOL3} = 5.0 \ \text{mA} \end{array}$			0.4	V
			$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \\ \text{IOL3} = 3.0 \ \text{mA} \end{array}$			0.4	V
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $\text{IOL3} = 2.0 \text{ mA}$			0.4	V

P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch open-Caution drain mode.



Items	Symbol	Conditi	000		MIN.	TYP.	MAX.	Unit
Input leakage cur- rent, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVDD0				1	μA
	ILIH2	P20 to P27, P137, RESET	VI = VDD				1	μA
	Іцнз	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator con- nection			10	μA
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso				-1	μA
	ILIL2	P20 to P27, P137, RESET	VI = Vss				-1	μA
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator con- nection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso	, In input port	10	20	100	kΩ

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(5/5)



3.3.2 Supply current characteristics

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	VDD = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fiн = 32 MHz ^{Note 3}	operation	VDD = 3.0 V		2.4		1
Note 1				fносо = 32 MHz,	Basic	VDD = 5.0 V		2.1		1
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.1		1
			HS (high-speed main)	fносо = 64 MHz,	Normal	Vdd = 5.0 V		5.2	9.3	mA
			mode Note 5	fiн = 32 MHz ^{Note 3}	operation	VDD = 3.0 V		5.2	9.3	
				fносо = 32 MHz,	Normal	VDD = 5.0 V		4.8	8.7	1
				fiн = 32 MHz Note 3	operation	VDD = 3.0 V		4.8	8.7	1
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.1	7.3	1
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		4.1	7.3	1
				fносо = 24 MHz,	Normal	VDD = 5.0 V		3.8	6.7	1
				fiн = 24 MHz Note 3	operation	VDD = 3.0 V		3.8	6.7	1
			fносо = 16 MHz, Norma	Normal	VDD = 5.0 V		2.8	4.9	1	
		fiн = 16 MHz Note 3	operation	VDD = 3.0 V		2.8	4.9	1		
		HS (high-speed main)	fmx = 20 MHz Note 2,	Normal	Square wave input		3.3	5.7	mA	
	mode Note 5	VDD = 5.0 V	operation	Resonator connection		3.5	5.8			
			fmx = 20 MHz Note 2,	Normal	Square wave input		3.3	5.7]	
				V _{DD} = 3.0 V	operation	Resonator connection		3.5	5.8]
				f _{MX} = 10 MHz Note 2,NormalVDD = 5.0 Voperation	Square wave input		2.0	3.4	1	
					operation	Resonator connection		2.1	3.5	-
				fmx = 10 MHz ^{Note 2} , VDD = 3.0 V	Normal operation	Square wave input		2.0	3.4	
						Resonator connection		2.1	3.5	
				fsub = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μA
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	1
				fsub = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	1
				TA = +25°C	operation	Resonator connection		4.7	6.1	1
				fsub = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	1
				TA = +50°C	operation	Resonator connection		4.8	6.7	-
			fsub = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	1	
				TA = +70°C	operation	Resonator connection		4.8	7.5	1
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	1
				TA = +85°C	operation	Resonator connection		5.4	8.9	1
				fsub = 32.768 kHz Note 4	Normal	Square wave input	1	7.2	21.0	1
				TA = +105°C	operation	Resonator connection		7.3	21.1	1

(TA = -40 to +105°C	. 2.4 V < EVDD0 < VDD -	\leq 5.5 V, Vss = EVsso = 0 V)
17 4010 100 0	, =	



(Notes and $\ensuremath{\textit{Remarks}}$ are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 5.Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.HS (high-speed main) mode: $2.7 V \le V D D \le 5.5 V @1 MHz$ to 32 MHz $2.4 V \le V D D \le 5.5 V @1 MHz$ to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- **Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



	. 100 0	, === = = =	$DD0 \leq VDD \leq 5.5 V,$						(2/2)
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	Idd2	HALT mode	HS (high-speed main)	fносо = 64 MHz,	V _{DD} = 5.0 V		0.80	4.36	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	V _{DD} = 3.0 V		0.80	4.36	1
				fносо = 32 MHz,	V _{DD} = 5.0 V		0.54	3.67	1
				fiн = 32 MHz Note 4	V _{DD} = 3.0 V		0.54	3.67	1
				fносо = 48 MHz,	V _{DD} = 5.0 V		0.62	3.42	1
				fiн = 24 MHz Note 4	V _{DD} = 3.0 V		0.62	3.42	1
				fносо = 24 MHz,	VDD = 5.0 V		0.44	2.85	
				fiH = 24 MHz Note 4	V _{DD} = 3.0 V		0.44	2.85	
				fносо = 16 MHz,	VDD = 5.0 V		0.40	2.08	
				fiн = 16 MHz Note 4	V _{DD} = 3.0 V		0.40	2.08	
			HS (high-speed main)	f _{MX} = 20 MHz Note 3,	Square wave input		0.28	2.45	mA
			mode Note 7	VDD = 5.0 V	Resonator connection		0.49	2.57	
				fmx = 20 MHz Note 3,	Square wave input		0.28	2.45	
				VDD = 3.0 V	Resonator connection		0.49	2.57	
			fmx = 10 MHz Note 3,	Square wave input		0.19	1.28		
			VDD = 5.0 V	Resonator connection		0.30	1.36		
				· · · · ·	Square wave input		0.19	1.28	4
			VDD = 3.0 V	Resonator connection		0.30	1.36		
			Subsystem clock	,	Square wave input		0.25	0.57	μA
			operation		Resonator connection		0.44	0.76	
				fsub = 32.768 kHz Note 5, TA = +25°C fsub = 32.768 kHz Note 5,	Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
					Square wave input		0.36	1.17	
				TA = +50°C	Resonator connection		0.59	1.36	
				fsub = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				TA = +70°C	Resonator connection		0.72	2.16	
				fsub = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				TA = +85°C	Resonator connection		1.16	3.56	
				fsub = 32.768 kHz Note 5,	Square wave input		3.20	17.10	
				TA = +105°C	Resonator connection		3.40	17.50	
	IDD3	STOP mode	Ta = -40°C	·			0.18	0.51	μA
	Note 6	Note 8	TA = +25°C				0.24	0.51]
			TA = +50°C				0.29	1.10	1
			T _A = +70°C				0.41	1.90	
			TA = +85°C				0.90	3.30	
			TA = +105°C				3.10	17.00	

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)

(Notes and Remarks are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. During HALT instruction execution by flash memory.
- **Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ @1 MHz to 32 MHz
 - $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 16 MHz
- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- **Remark 3.** fill: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscilla- tor operating current	I _{FIL} Note 1				0.2		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operat- ing current	I _{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μA
A/D converter operating cur- rent	I _{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	ADREF Note 1				75		μA
Temperature sensor operat- ing current	ITMPS Note 1				75		μA
D/A converter operating cur- rent	IDAC Notes 1, 11	Per D/A converter channel				1.5	mA
PGA operating current		Operation			480	700	μA
Comparator operating cur- rent	ICMP Notes 1, 12	Operation (per comparator chan- nel, constant current for compara-	When the internal reference voltage is not in use		50	100	μA
		tor included)	When the internal reference voltage is in use		60	110	μA
LVD operating current	I _{LVD} Notes 1, 7				0.08		μA
Self-programming operat- ing current	IFSP Notes 1, 9				2.50	12.2	mA
BGO operating current	IBGO Notes 1, 8				2.50	12.2	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion opera- tions are performed, Low volt- age mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	2.04	
		CSI/UART operation			0.70	1.54	
		DTC operation			3.10		

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 ') V)
--	------

Note 1. Current flowing to VDD.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

- **Note 3.** Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **Note 7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing during programming of the data flash.
- **Note 9.** Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 26.3.3 SNOOZE mode in the RL78/G1F User's Manual.

- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C



3.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Тсү	Main system	HS (high-speed main)	$2.7~V \leq V\text{DD} \leq 5.5~V$	0.03125		1	μs
imum instruction exe- cution time)		clock (fmain) operation	mode	$2.4~V \leq V_{DD} < 2.7~V$	0.0625		1	μs
		Subsystem clo	ock (fsuв) operation	$2.4~V \leq V \text{DD} \leq 5.5~V$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \leq V_{DD} \leq 5.5~V$	0.03125		1	μs
		program- ming mode	mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	0.0625		1	μs
External system clock	fEX	$2.7~V \leq V \text{DD} \leq$	5.5 V		1.0		20.0	MHz
frequency		$2.4~V \leq V \text{DD} \leq$	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7~V \leq V \text{DD} \leq$	5.5 V		24			ns
input high-level width,	texL	$2.4~V \leq V_{DD} \leq$	2.7 V		30			ns
low-level width	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low- level width	ttiH, tti∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7~V \leq EV_{DD0} \leq 5.5~V$	100			ns
				$2.4~V \leq EV_{DD0} < 2.7~V$	300			ns
Timer RJ input high-	tтлн,	TRJIO		$2.7~V \leq EV \text{DD0} \leq 5.5~V$	40			ns
level width, low-level width	t⊤ji∟			$2.4 \text{ V} \leq \text{EVdd0} < 2.7 \text{ V}$	120			ns

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Note The following conditions are required for low voltage interface when EVDD0 < VDD

2.4 V \leq EVDD0 < 2.7 V: MIN. 125 ns

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))



$(1A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V})$	i					i	(2/2)
Items	Symbol	Conditio	ons	MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	ttdih, ttdi∟	TRDIOA0, TRDIOA1, TRDIOE TRDIOC0, TRDIOC1, TRDIO		3/fc∟к			ns
Timer RD forced cutoff signal	TDSIL	P130/INTP0	$2MHz < fclk \le 32 MHz$	1			μs
input low-level width			fclk ≤ 2 MHz	1/fclk + 1			
Timer RG input high-level width, low-level width	tтGін, tтGі∟	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03,	fто	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
TRJIO0, TRJO0,			$2.7 \text{ V} \leq EV_{DD0} < 4.0 \text{ V}$			8	MHz
TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1,			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$				
TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency						4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-speed main) mode	$4.0~V \leq EV \text{DD0} \leq 5.5~V$			16	MHz
frequency			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
Interrupt input high-level	tinth,	INTP0	$2.4~V \leq V\text{DD} \leq 5.5~V$	1			μs
width, low-level width	tintl	INTP1 to INTP11	$2.4~V \leq EV \text{DD0} \leq 5.5~V$	1			μs
Key interrupt input low-level width	tkr	KR0 to KR7	$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsl			10			μs

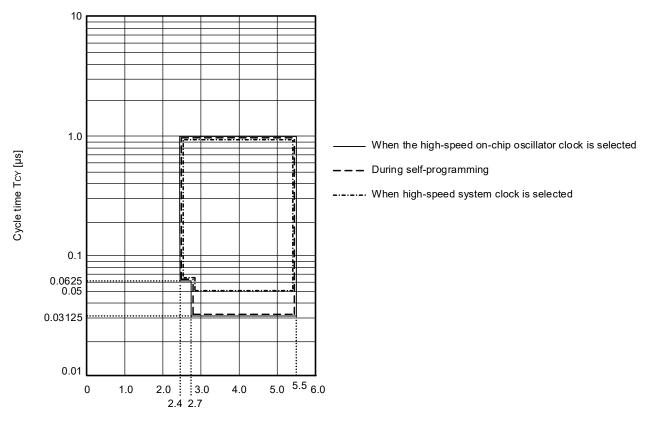
(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)



Minimum Instruction Execution Time during Main System Clock Operation

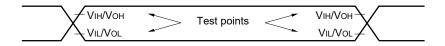
TCY vs VDD (HS (high-speed main) mode)



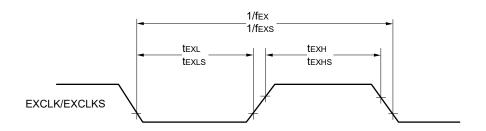
Supply voltage VDD [V]



AC Timing Test Points

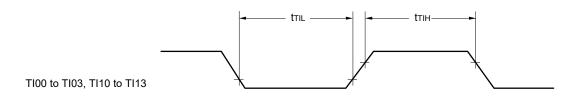


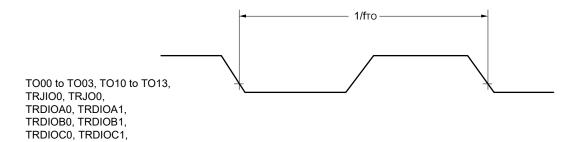
External System Clock Timing



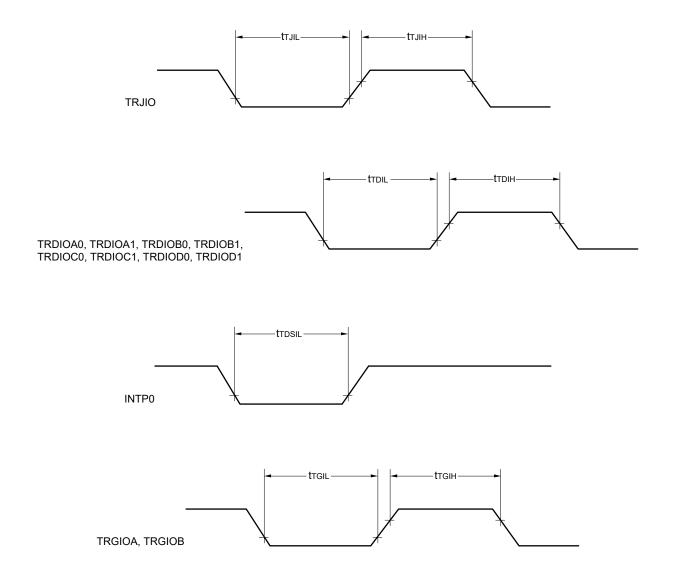
TI/TO Timing

TRDIOD0, TRDIOD1, TRGIOA, TRGIOB









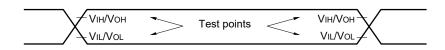


RESET



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		
			MIN.	MAX.	
Transfer rate		$2.4~V \leq EV_{DD0} \leq 5.5~V$		fмск/12 Note 2	bps
Note 1		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps
		in the SNOOZE mode is 480		•	

 However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

 Note 2.
 The following conditions are required for low voltage interface when EVDD0 < VDD.</td>

 2.4 V ≤ EVDD0 < 2.7 V: MAX.1.3 Mbps</td>

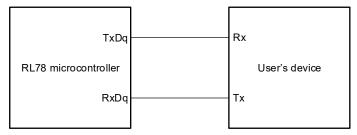
 Note 3.
 The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

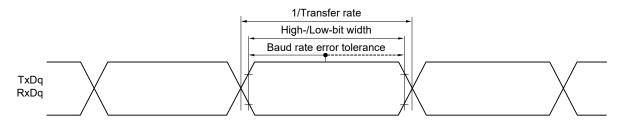
Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed	HS (high-speed main) mode	
					MAX.	
SCKp cycle time	t КСҮ1	$t_{KCY1} \geq 2/f_{CLK}$	$2.7~V \leq EV_{DD0} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tкнı,	4.0 V ≤ EVDD0 ≤ 5.5 V tKCY1/2		tксү1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 36		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 76		
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0~V \leq EV_{DD0} \leq 5.5~V$		66		ns
		$2.7 \text{ V} \leq EV_{DD0} \leq 8$	5.5 V	66		ns
		$2.4~V \leq EV_{DD0} \leq 5.5~V$		113		
SIp hold time (from SCKp [↑]) Note 2	tksi1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tксү2	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	20 MHz < fмск	16/fмск		ns
			fмск ≤ 20 MHz	12/fмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$	16 MHz < fмск	16/fмск		ns
			fмск \leq 16 MHz	12/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		12/fмск and 1000		ns
1 0	tкн2, tкL2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tксү2/2 - 14		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү2/2 - 16		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		1/fмск + 36		ns
SIp setup time tsik₂ (to SCKp↑) Note 1	tsik2	$2.7~V \leq EV_{DD0} \leq 5.5~V$		1/fмск + 40		ns
		$2.4~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 60		ns	
Slp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output _{Note 3}	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 66	ns
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



Note 4. C is the load capacitance of the SOp output lines.

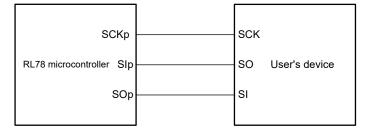
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)(2/2)

Parameter	Symbol	Conditions		HS (high-speed ma	HS (high-speed main) mode	
				MIN.	MAX.	
SSI00 setup time	tSSIK	DAPmn = 0	$2.7~V \leq EV_{DD0} \leq 5.5~V$	240		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	400		ns
		DAPmn = 1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 240		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 400		ns
SSI00 hold time	DAPmn = 0	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 240		ns	
		$2.4~V \leq EV_{DD0} \leq 5.5~V$	1/fмск + 400		ns	
		DAPmn = 1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	240		ns
			$2.4~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$	400		ns

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)

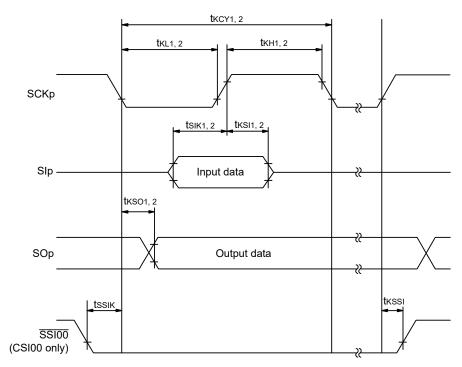


CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))

SCK00	SCK
SI00 RL78 microcontroller	SO User's device
SO00	SI
<u>SS100</u>	SSO

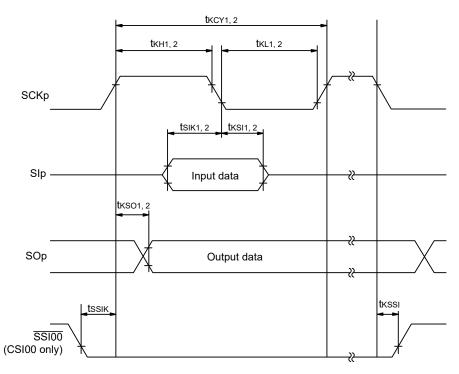
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

(4) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions	HS (high-speed	HS (high-speed main) mode	
			MIN.	MAX.	
SCLr clock frequency	fsc∟	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{\text{DD0}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$		400 Note 1	kHz
		$\label{eq:loss} \begin{array}{l} \mbox{2.4 V} \leq EV_{\text{DD0}} \leq 5.5 \mbox{ V}, \\ \mbox{C}_{b} = 100 \mbox{ pF}, \mbox{ R}_{b} = 3 \kappa\Omega \end{array}$		100 Note 1	kHz
Hold time when SCLr = "L"	t∟ow	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1200		ns
		$\label{eq:loss} \begin{array}{l} \mbox{2.4 V} \leq EV_{\text{DD0}} \leq 5.5 \mbox{ V}, \\ \mbox{C}_{b} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{b} \mbox{=} 3 \mbox{Ω} \end{array}$	4600		ns
Hold time when SCLr = "H"	tніgн	$\label{eq:constraint} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \Omega \end{array}$	1200		ns
		$\label{eq:loss} \begin{array}{l} \mbox{2.4 V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ \mbox{C}_{b} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{b} \mbox{=} 3 \mbox{Ω} \end{array}$	4600		ns
Data setup time (reception)	tsu: dat	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1/fмск + 220 Note 2		ns
		$\label{eq:loss} \begin{array}{l} \mbox{2.4 V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ \mbox{C}_{b} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{b} \mbox{=} 3 k\Omega \end{array}$	1/fмск + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$\label{eq:states} \begin{array}{l} 2.7 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	770	ns
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{array}$	0	1420	ns

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{EVDD0} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = 0 \text{ V})$

Note 1. The value must also be equal to or less than fMCK/4.

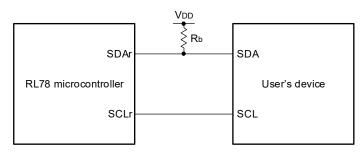
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

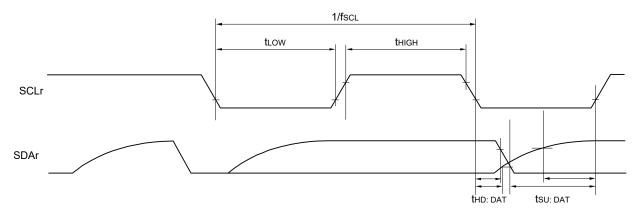
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remark 1.** $R_b[\Omega]$: Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21), g: PIM number (g = 0, 1, 3, 5, 7),
- h: POM number (h = 0, 1, 3, 5, 7)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10, 11)



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

$T_{A} = -40 \text{ to } \pm 105^{\circ}\text{C}$	24V < FV	< Vnn < 5 5 V	Vss = EVsso = 0 V)	١
IA = -40 10 + 100 0	', ∠.┭v ≤ ∟∨∪∪∪	\geq VDD \geq 0.0 V,	v 33 - Lv 330 - 0 v j	,

(1/2)

Parameter	Symbol		Conditions		HS (high-s	peed main) mode	Unit
					MIN.	MAX.	
Transfer rate		reception	$\begin{array}{l} 4.0 \; V \leq E V_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$			f _{MCK} /12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps
				$\label{eq:V} \begin{split} V &\leq EV_{DD0} < 4.0 \text{ V}, \\ V &\leq V_b \leq 2.7 \text{ V} \end{split}$		fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps
				$\label{eq:V} \begin{array}{l} V \leq EV_{DD0} < 3.3 \ V, \\ V \leq V_{b} \leq 2.0 \ V \end{array}$		fмск/12 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		1.3	Mbps

 Note 1.
 Transfer rate in the SNOOZE mode is 4800 bps only.

 However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4~V \leq EV\text{DD0} < 2.7~V\text{:}$ MAX. 2.6 Mbps

 $1.8~V \leq EV\text{DD0} < 2.4~V:$ MAX. 1.3 Mbps

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- Remark 1. Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C	$2.4 V \le EVDD0 \le VDD \le 5.5 V$, VSS = EVSS0 =	: 0 V)
(/

(2/2)

Parameter	Symbol	bol Conditions	Conditions	HS (high-speed main) mode		Unit
				MIN.	MAX.	-
Transfer rate		transmission	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.6 Note 2	Mbps
			$\label{eq:V_var} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, \text{R}_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note 4	Mbps
			$\label{eq:V} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega,$ $V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}\text{DD0} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate}} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times 100 \text{ [\%]}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 2.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EVDD0 < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$

1

$$\text{ud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate } \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Maximum transfer

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Note 5. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

1

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

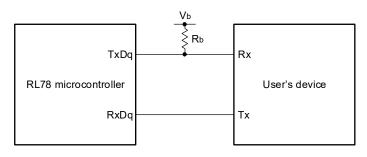
* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 6.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

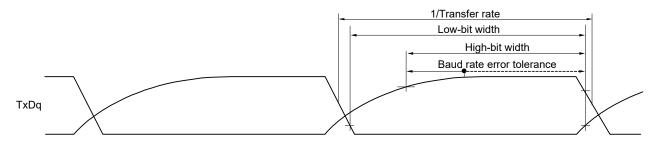
(Remarks are listed on the next page.)

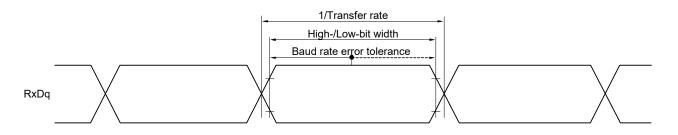


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remark 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1, 5, 7)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	C	Conditions	HS (high-speed	d main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 4/fclк		600		ns
			$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1000		ns
			$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	2300		ns
SCKp high-level width	evel width tkH1			tkcy1/2 - 150		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tkcy1/2 - 340		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \end{array}$,	tkcy1/2 - 916		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \\ \hline \\ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq EV_{DD0} < 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tксү1/2 - 24		ns
				tксү1/2 - 36		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		tксү1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

$(T_{A} = -4$	0 to +105°C.	1.8 V < EVDD0	< VDD < 5.5 V.	Vss = EVsso = 0 V)
(IA = -7	$\sim 100 \cdot 100 \circ$,		_ v b b _ v.v v,	v o o = o v j

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	HS (high-speed main) mode	
			MIN.	MAX.	
Slp setup time (to SCKp↑) ^{Note}	tsıĸı		162		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	354		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksi1		38		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	38		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		390	ns
		$\label{eq:VD} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(**Remarks** are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

1	$T_{A} = -40$ to $\pm 105^{\circ}C$.	1.8 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)	
	$1 - 40 10 \cdot 100 0$		

(3/3)

Parameter	Symbol	Conditions	HS (high-spee	HS (high-speed main) mode	
			MIN.	MAX.	
Slp setup time (to SCKp↓) ^{Note}	tsıĸı		88		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	88		ns
		$\label{eq:VDD0} \begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	220		ns
SIp hold time (from SCKp \downarrow) ^{Note}	tksi1		38		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	38		ns
		$\label{eq:VDD0} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1			50	ns
		$\begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		50	ns
		$\label{eq:V} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		50	ns

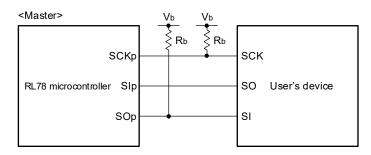
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(**Remarks** are listed on the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential



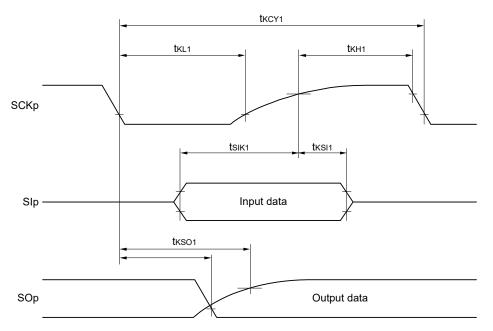
Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

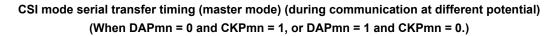
Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

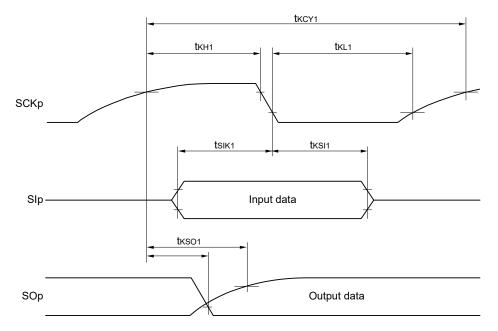
Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Remark 3. Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)

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(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Cor	nditions	HS (high-spe	ed main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tксү2	$4.0~V \leq EV_{DD0} \leq 5.5~V,$	24 MHz < fмск	28/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	$20 \text{ MHz} < f_{MCK} \leq 24 \text{ MHz}$	24/fмск		ns
			$8 \text{ MHz} < \text{fmck} \leq 20 \text{ MHz}$	20/fмск		ns
			$4 \text{ MHz} < \text{fmck} \leq 8 \text{ MHz}$	16/fмск		ns
			fмск \leq 4 MHz	12/fмск		ns
		$2.7~V \leq EV_{DD0} < 4.0~V,$	24 MHz < fмск	40/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	$20 \text{ MHz} < f_{MCK} \leq 24 \text{ MHz}$	32/fмск		ns
			$16 \; MHz < f_{MCK} \leq 20 \; MHz$	28/fмск		ns
			$8 \text{ MHz} < \text{fmck} \leq 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < f_{MCK} \leq 8 \text{ MHz}$	16/fмск		ns
			fмск \leq 4 MHz	12/fмск		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$	24 MHz < fмск	96/fмск		ns
			$20 \text{ MHz} < f_{MCK} \leq 24 \text{ MHz}$	72/fмск		ns
			$16 \; MHz < f_{MCK} \leq 20 \; MHz$	64/fмск		ns
			$8 \text{ MHz} < \text{fmck} \leq 16 \text{ MHz}$	52/fмск		ns
			$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	32/fмск		ns
			fмск \leq 4 MHz	20/fмск		ns
SCKp high-/low-level	tкн2, tк∟2	$4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V$		tkcy2/2 - 24		ns
width		$2.7~\text{V} \leq E\text{V}_{DD0} < 4.0~\text{V},~2.3~\text{V} \leq \text{V}_b \leq 2.7~\text{V}$		tkcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.$	$6~V \leq V_b \leq 2.0~V$	tксү2/2 - 100		ns
SIp setup time	tsik2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.$	$3~V \leq V_b \leq 2.7~V$	1/fмск + 40		ns
(to SCKp↑) Note 2		$2.4 \text{ V} \le EV_{DD0} < 3.3 \text{ V}, 1.$	$6~V \leq V_b \leq 2.0~V$	1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 3}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	tkso2	$\begin{array}{l} 4.0 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \ 2. \\ \text{C}_{\text{b}} = 30 \ \text{pF}, \ \text{R}_{\text{b}} = 1.4 \ \text{k}\Omega \end{array}$	$7~V \leq V_b \leq 4.0~V,$		2/fмск + 240	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \ 2. \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	$3~V \leq V_b \leq 2.7~V,$		2/fмск + 428	ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \ 1. \\ C_b = 30 \ pF, \ R_v = 5.5 \ k\Omega \end{array}$	$6~V \leq V_b \leq 2.0~V,$		2/fмск + 1146	ns

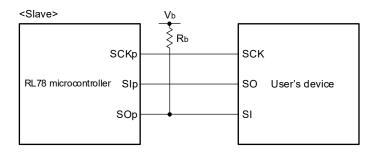
(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(Notes and Remarks are listed on the next page.)



- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 48, 32, 24-pin products)/EVDD tolerance (for the 64, 36-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

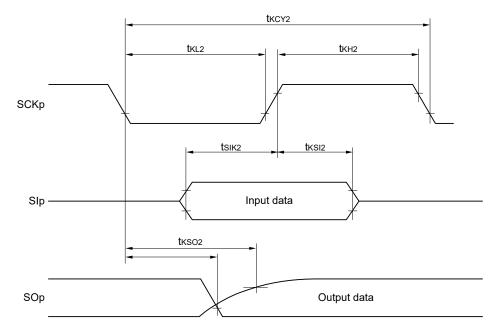
CSI mode connection diagram (during communication at different potential)



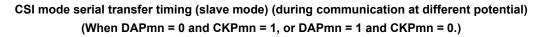
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10))
- Remark 4. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the

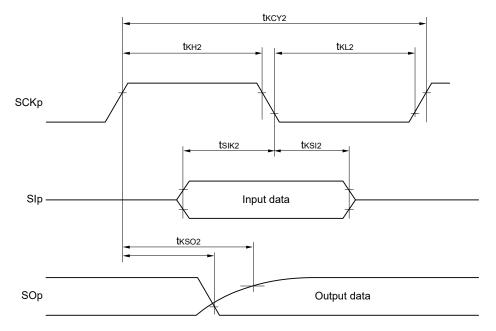
Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark 1. p: CSI number (p = 00, 01, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3, 5, 7)

Remark 2. CSI01 of 48-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit	
			MIN.	MAX.		
SCLr clock frequency	fscL			400 Note 1	kHz	
		$\label{eq:Vb} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1	kHz	
				100 Note 1	kHz	
		$\label{eq:Vb} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		100 Note 1	kHz	
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		100 Note 1	kHz	
Hold time when SCLr = "L"	tLow		1200		ns	
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns	
			4600		ns	
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	4600		ns	
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_{b} \leq 2.0 \ V, \\ C_{b} = 100 \ pF, \ R_{b} = 5.5 \ k\Omega \end{array}$	4650		ns	
Hold time when SCLr = "H"	tніgн		620		ns	
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		ns	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	2700		ns	
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 100 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	2400		ns	
		$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	1830		ns	

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C	. 2 4 V < FV	< V ס 5 5 V '	$V_{SS} = FV_{SS0} = 0 V$

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	ain) mode	Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat		1/f _{MCK} + 340 Note 2		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/f _{MCK} + 340 Note 2		ns
			1/f _{MCK} + 760 Note 2		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/f _{MCK} + 760 Note 2		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \; V \leq E \; V_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	1/f _{MCK} + 570 Note 2		ns
Data hold time (transmission)	thd:dat		0	770	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	770	ns
			0	1420	ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	1420	ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	0	1215	ns

Note 1. The value must also be equal to or less than fMCK/4.

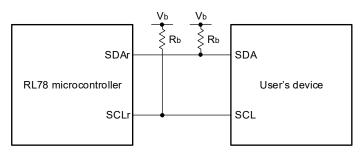
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

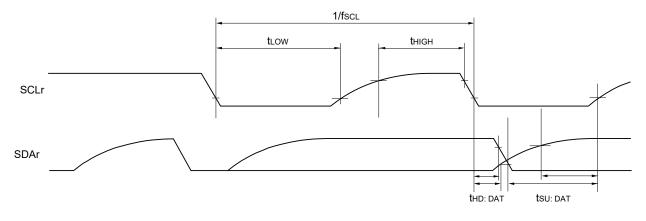
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01, 10, 11, 20), g: PIM, POM number (g = 0, 1, 3, 5, 7)
- **Remark 3.** fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10)



3.5.2 Serial interface IICA

((TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)
•		,

Parameter	Symbol	Conditions	HS	HS (high-speed main) mode			
			Standa	rd mode	Fast	Fast mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLĸ ≥ 3.5 MHz	-	—	0	400	kHz
		Standard mode: fcLκ ≥ 1 MHz	0	100	—	—	kHz
Setup time of restart condition	tsu: sta		4.7		0.6		μs
Hold time Note 1	thd: STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

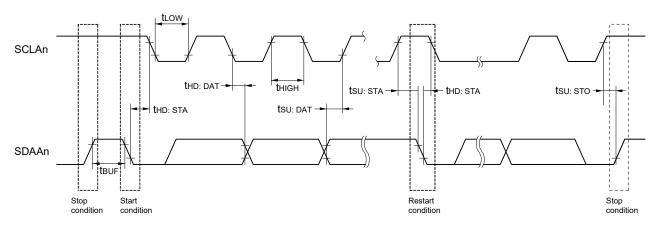
Note 2. The maximum value (MAX.) of tHD: DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

 $Standard mode: \quad C_b = 400 \ pF, \ R_b = 2.7 \ k\Omega \\ Fast mode: \quad C_b = 320 \ pF, \ R_b = 1.1 \ k\Omega \\$

IICA serial transfer timing



Remark n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI7	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI24	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP,
Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions	Conditions			MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \leq AV_{REFP} \leq 5.5~V$		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \le V_{DD} \le 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \le V_{DD} \le 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output volt-	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		age (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39 39 39 39 39 39 39 ±0.25 ±0.25 ±1.5	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \le AV_{REFP} \le 5.5~V$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI7		0		AVREFP	V
		$\begin{tabular}{lllllllllllllllllllllllllllllllllll$		/ _{BGR} Note	BGR Note 4		
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			MPS25 No	ie 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

 Note 3.
 When AVREFP < VDD, the MAX. values are as follows.</td>

 Overall error:
 Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

 Zero-scale error/Full-scale error:
 Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

 Integral linearity error/ Differential linearity error:
 Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

 Note 4.
 Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI24

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	solution RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$\begin{array}{c c} ANI20 \\ \hline & 3.6 \ V \leq V_{DD} \leq 5.5 \ V \\ \hline & 2.125 \\ \hline & 2.7 \ V \leq V_{DD} \leq 5.5 \ V \\ \hline & 3.1875 \\ \hline & 2.4 \ V \leq V_{DD} \leq 5.5 \ V \\ \hline & 17 \\ \hline & 2.4 \ V \leq AV_{REFP} \leq 5.5 \ V \\ \hline & \pm 0 \\ \hline \end{array}$	39	μs		
		Target ANI pin: ANI16 to ANI20	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V \text{DD} \leq 5.5~V$	17		10 ±5.0 39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$2.4~V \le AV_{REFP} \le 5.5~V$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI24		0		and	V

(Ta = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD0 \le AVREFP \le VDD$, the MAX. values are as follows.

	Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.				
	Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.				
	Integral linearity error/ Differential linearity error:	Add ±0.5 LSB to the MAX. value when AVREFP = VDD.				
Note 4.	5 , ,					
	Overall error:	Add ±4.0 LSB to the MAX. value when AVREFP = VDD.				

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VbD. Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AVREFP = VbD.



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI7, ANI16 to ANI24, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7~V \leq V_{DD} \leq 5.5~V$	8 V 1.2 V 2.125 V 3.1875 V 17 V 2.375 V 3.5625 V 17 V	39	μs	
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		(HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		10 ±7.0 39 39 39 39 39 39 39 39 39 39 39 39 ±0.60 ±0.60 ±4.0 ±2.0 VDD EVDD0	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI7		0		Vdd	V
		ANI16 to ANI24		1.2 ± 2.125 1 3.1875 1 17 1 2.375 1 3.5625 1 17 ± 17 ± 17 ± 17 ± 17 ± 17 ± 17 ± 10 ± 11 ± <tr< td=""><td>EV_{DD0}</td><td>V</td></tr<>	EV _{DD0}	V	
		Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) r	node)	VBGR Note 3		3	V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) r	node)	۲V	MPS25 Not	te 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI7, ANI16 to ANI24

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{EVDD0} \le \text{VDD}, \text{Vss} = \text{EVss0} = 0 \text{ V}, \text{Reference voltage (+)} = \text{VBGR}^{\text{Note 3}}, \text{Reference voltage (-)} = \text{AVREFM} = 0 \text{ V}^{\text{Note 4}}, \text{HS (high-speed main) mode}$

Parameter	Symbol	Conditions		MIN.	TYP. MAX.		Unit
Resolution	RES			8		bit	
Conversion time	tCONV	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V\text{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN		•	0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



RL78/G1F

3.6.2 Temperature sensor characteristics/internal reference voltage characteristic

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = EVsso = 0 V, HS (high-speed main) mode)

3.6.3 D/A converter characteristics

(TA = -40 to +105°C, 2.4 V \leq EVsso \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 M Ω	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
		Rload = 8 M Ω	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7~V \leq V_{DD} \leq 5.5~V$			3	μs
			$2.4~V \leq V_{DD} < 2.7~V$			6	μs



3.6.4 Comparator

Parameter	Symbol	Con	nditions	MIN.	TYP.	MAX.	Unit		
Input offset voltage	VIOCMP				±5	±40	mV		
Input voltage range	VICMP					Vdd	V		
Internal reference	ΔV_{IREF}	CmRVM register value : 7	FH to 80H (m = 0, 1)			±40	LSB		
voltage deviation Response Time		Other than above				±1	LSB		
Response Time	tcr, tcr	Input amplitude±100mV			70	150	ns		
Operation stabilization	tсмр	CMPn = 0→1	V _{DD} = 3.3 to 5.5 V			1	μs		
time ^{Note 1}			V _{DD} = 2.7 to 3.3 V			3	μs		
Reference voltage stabilization wait time	tvr	CVRE : 0→1 ^{Note 2}				20	μs		
Operation current	ICMPDD	Separately, it is defined as	the operation current of perip	heral function	ons.	±1 L3 70 150 r 1 μ 3 μ			

 $(TA = -40 \text{ to } +105^{\circ}C, 2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Note 1. Time taken until the comparator satisfies the DC/AC characteristics after the comparator operation enable signal is switched (CMPnEN = $0 \rightarrow 1$).

Note 2. Enable comparator output (CnOE bit = 1; n = 0 to 1) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 1) and waiting for the operation stabilization time to elapse.

3.6.5 PGA

TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	Vipga			0		0.9 × V _{DD} / Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{\text{DD}}$			V
	VIOLPGA					$0.07\times V_{\text{DD}}$	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32				±2	%
Slew rate	SRrpga	Rising When Vin= 0.1V₀₀/gain to 0.9V₀₀/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
		10 to 90% of output	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
	SRfpga	Falling When Vin= 0.1Vpb/gain to 0.9Vpb/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		90 to 10% of output	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time- Note 1		x16, x32				10	μs
Operation current	PGADD	Separately, it is defined a	is the operation current of per	ipheral function	ons.		

Note 1. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

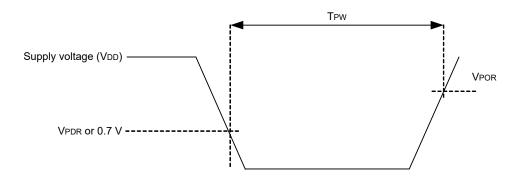
3.6.6 POR circuit characteristics

(TA = -40 to +105°C, Vss = 0 V	(TA	= -40 t	o +105°C.	Vss = 0 V
--------------------------------	-----	---------	-----------	-----------

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.45	1.51	1.55	V
	VPDR	Voltage threshold on VDD falling Note 1	1.44	1.50	1.54	V
Minimum pulse width Note 2	TPW		300			μs

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in **3.4 AC Characteristics**.

Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPDR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





3.6.7 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	3.90	4.06	4.22	V
threshold			Falling edge	3.83	3.98	4.13	V
		VLVD1	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		Vlvd2	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
		Vlvd3	Rising edge	2.90	3.02	3.14	V
			Falling edge	2.85	2.96	3.07	V
		VLVD4	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		VLVD5	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		VLVD6	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		VLVD7	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse wid	lth	t∟w		300			μs
Detection delay tin	ne					300	μs



Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, fa	c2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage				V
threshold	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

(2) Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

3.6.8 **Power supply voltage rising slope characteristics**

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

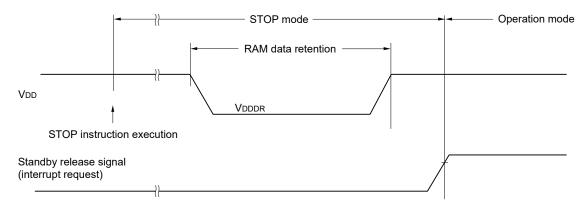
3.7 RAM Data Retention Characteristics

(TA = -40 to +105°C, Vss = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Notes 1, 2		5.5	V

Note 1. The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



3.8 Flash Memory Programming Characteristics

(Ta = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4~V \leq V_{DD} \leq 5.5~V$	1		32	MHz



(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditior	าร	MIN.	TYP.	MAX.	Unit
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	Ta = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

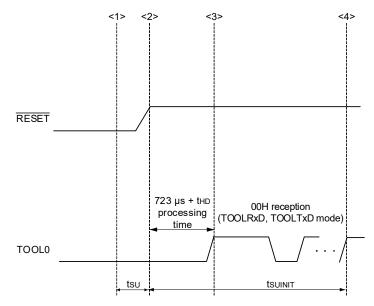
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



RL78/G1F

3.10 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How love until all external reset ends How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

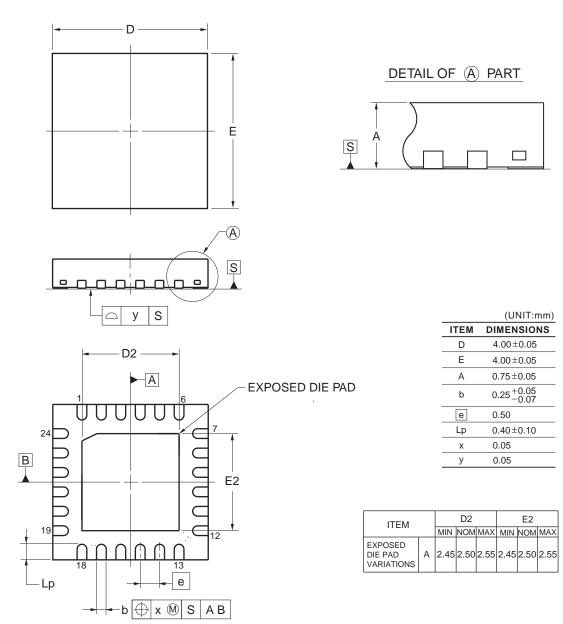
- tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
- tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



4. PACKAGE DRAWINGS

4.1 24-pin products

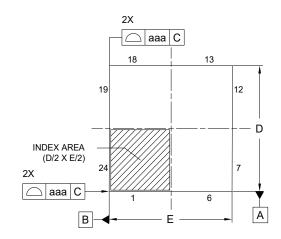
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04

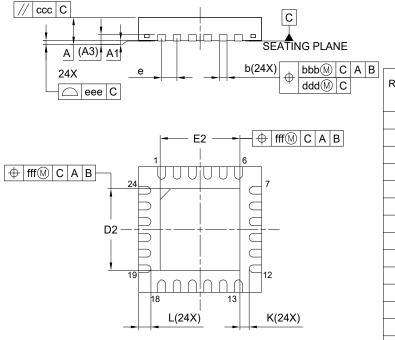


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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN024-4x4-0.50	PWQN0024KF-A	0.04





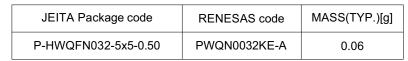
Reference	Dimens	sion in Milli	meters
Symbol	Min.	Nom.	Max.
А	-	-	0.80
A1	0.00	0.02	0.05
A3	(0.203 REF	
b	0.18	0.25	0.30
D	4.00 BSC		
Е	4.00 BSC		
е	0.50 BSC		
L	0.35 0.40 0.4		0.45
К	0.20	-	-
D2	2.55	2.60	2.65
E2	2.55	2.60	2.65
aaa		0.15	
bbb		0.10	
CCC		0.10	
ddd		0.05	
eee		0.08	
fff	0.10		

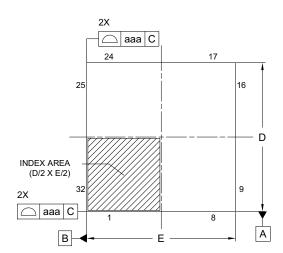


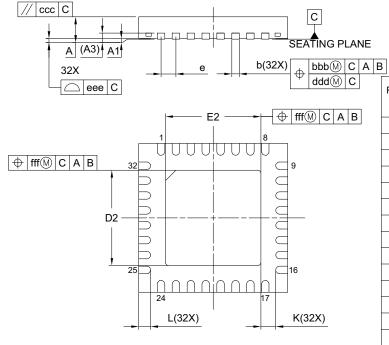
RL78/G1F

4.2 32-pin products

<R>

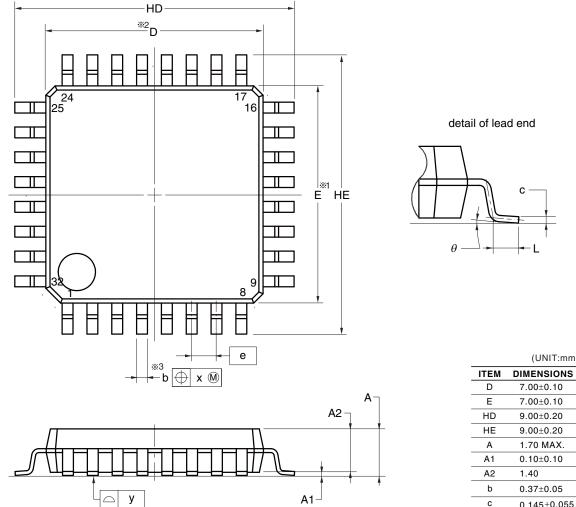






Reference	Dimen	sion in Milli	meters
Symbol	Min.	Nom.	Max.
А	_	-	0.80
A ₁	0.00	0.02	0.05
A ₃	(0.203 REF	
b	0.18	0.25	0.30
D		5.00 BSC	
Е	5.00 BSC		
е	0.50 BSC		
L	0.35	0.40	0.45
К	0.20	-	-
D ₂	3.15	3.20	3.25
E2	3.15	3.20	3.25
aaa		0.15	
bbb		0.10	
CCC		0.10	
ddd		0.05	
eee		0.08	
fff		0.10	

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2



(UNIT:mm)

D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
А	1.70 MAX.
A1	$0.10 {\pm} 0.10$
A2	1.40
b	$0.37{\pm}0.05$
с	0.145 ± 0.055
L	0.50±0.20
θ	0° to 8°
е	0.80
х	0.20
У	0.10

NOTE

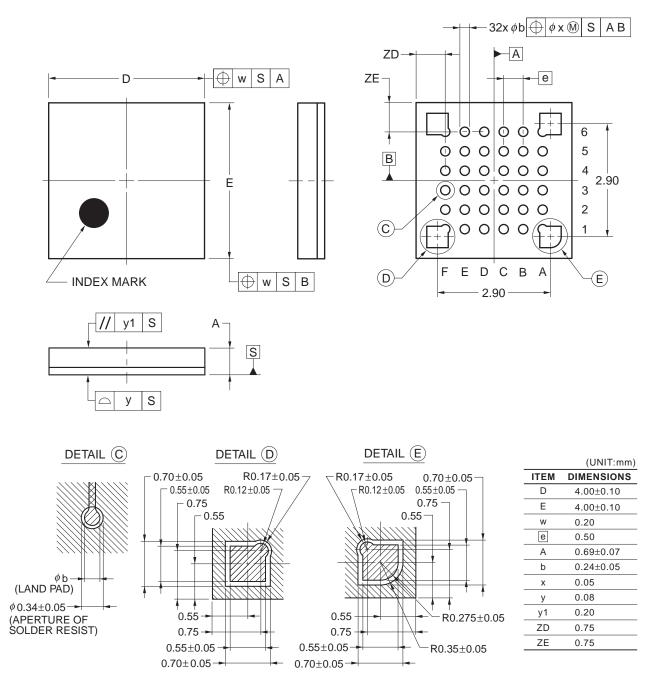
1.Dimensions "%1" and "%2" do not include mold flash.

2.Dimension "%3" does not include trim offset.



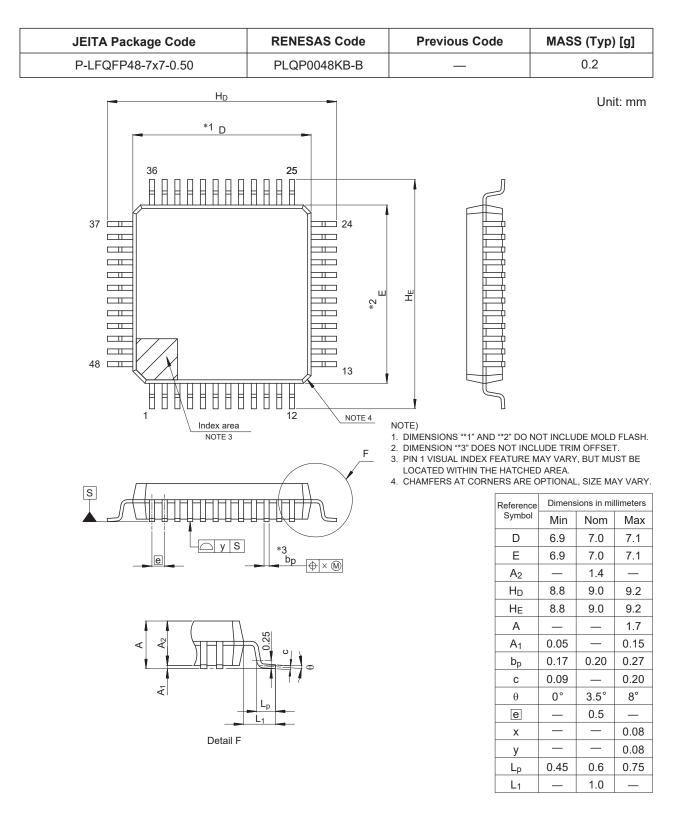
4.3 36-pin products

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50 PWLG0036KA-A		P36FC-50-AA4-2	0.023





4.4 48-pin products

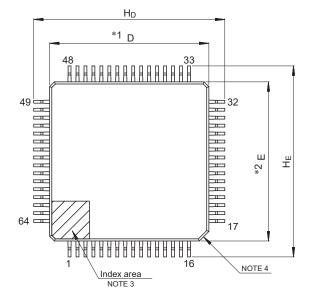


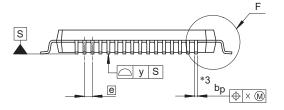
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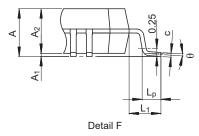


64-pin products 4.5

JEITA Package Code RENESAS Code		Previous Code	MASS (Typ) [g]
P-LFQFP64-10x10-0.50	PLQP0064KB-C	_	0.3





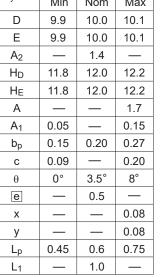


DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
 DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

- 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
- 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference	Dimens	ions in mi	llimeters
Symbol	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A ₂	—	1.4	—
H_{D}	11.8	12.0	12.2
HE	11.8	12.0	12.2
А	—	_	1.7
A ₁	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09		0.20
θ	0°	3.5°	8°
е	—	0.5	_
х		_	0.08
у		_	0.08
Lp	0.45	0.6	0.75
L ₁	—	1.0	_

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Unit: mm

REVISION HISTORY

RL78/G1F Datasheet

Dav	Dete		Description
Rev.	Date	Page	Summary
0.10		—	First Edition issued
0.50	Jan 14, 2015	3	Modification of description in Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1F
		10	Addition of description in 1.4 Pin Identification
		11	Modification of description in 1.5 Block Diagram
		12, 13	Modification of description in 1.6 Outline of Functions
		14	Addition of target products to the beginning
		17	Modification of 2.2.2 On-chip oscillator characteristics
		18	Addition of note 4 in 2.3.1 Pin characteristics
		23, 25, 27	Modification of 2.3.2 Supply current characteristics
		73	Modification of 2.6.4 Comparator
		73	Modification of 2.6.5 PGA
		77	Renamed to 2.7 RAM Data Retention Characteristics
		79	Addition of target products to the beginning
		83	Modification of 3.2.2 On-chip oscillator characteristics
		87	Modification of "Output voltage, low"
		89, 91, 93	Modification of 3.3.2 Supply current characteristics
		130	Modification of 3.6.4 Comparator
		130	Modification of 3.6.5 PGA
		133	Renamed to 3.7 RAM Data Retention Characteristics
1.00	Jan 14, 2015	All	Modification of the unit symbol (PWMOP into PWMOPA)
		1	Modification of descriptions in 1.1 Features
		10	Modification of 1.4 Pin Identification
		13	Modification of 1.6 Outline of Functions
		73	Modification of 2.6.5 PGA
		130	Modification of 3.6.5 PGA
1.10	Aug 12, 2016	5	Addition of product name (RL78/G1F) and description (Top View) in 1.3.1 24-pin products
		6	Addition of product name (RL78/G1F) and description (Top View) in 1.3.2 32-pin products
		8	Addition of product name (RL78/G1F) and description (Top View) in 1.3.4 48-pin products
		9	Addition of product name (RL78/G1F) and description (Top View) in 1.3.5 64-pin products
1.11	Dec 22, 2020	3	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G1F
		4	Addition of title and modification of description in Table 1-1 List of Ordering Part Numbers
		136 to 141	Addition and modification of all in CHAPTER 39 PACKAGE DRAWINGS
		10010141	

Rev.	Date	Description	
		Page	Summary
1.12	Apr 28, 2021	4	Modification of Table 1 - 1 List of Ordering Part Numbers
		6	Addition of 32-pin plastic HWQFN (5 × 5 mm, 0.5-mm pitch) in 1.3.2 32-pin products
		139	Addition of package drawing of PWQN0032KE-A in 4.2 32-pin products

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The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{II} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a systemevaluation test for the given product.

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